Available online at www.sciencedirect.com
SCIENCE DIRECT®
NIM B
Beam Interactions with Materials & Atoms
ELSEVIER
Nuclear Instruments and Methods in Physics Research B 206 (2003) 1128–1153
www.elsevier.com/locate/nimb

Author index

Abdalla, M., see Marchal, J. . . . 206 (2003) 462
Abe, H., H. Uchida, Y. Azuma, A. Uedono, Z.Q. Chen and H. Itoh, Improvement of hydrogen absorption rate of Pd by ion irradiation . . . 206 (2003) 224
Abe, H., see Kasukabe, Y. . . . 206 (2003) 390
Abe, H., see Vacik, J. . . . 206 (2003) 395
Abe, H., see Hirao, T. . . . 206 (2003) 457
Abe, K., O. Eryu, O. Kogi and K. Nakashima, Electrical properties of high-dose nitrogen-implanted and rapid thermal annealed 6H–SiC . . . 206 (2003) 960
Abe, K., see Eryu, O. . . . 206 (2003) 969
Abe, T., see Morishita, T. . . . 206 (2003) 565
Abramof, E., see Ueda, M. . . . 206 (2003) 749
Adachi, K., see Tsuji, H. . . . 206 (2003) 615
Adachi, K., see Arai, N. . . . 206 (2003) 629
Afanasyev-Charkin, I.V. and M. Nastasi, Dependence of optical properties and hardness on carbon content in silicon carbonitride films deposited by plasma ion immersion processing technique . . . 206 (2003) 736
Ahmed, S., B.J. Sealy and R. Gwilliam, Effect of proton implantation at variable temperatures and doses on the semi-insulating GaAs . . . 206 (2003) 1003
Ahmed, S., B.J. Sealy and R. Gwilliam, Annealing characteristics of the implant-isolated n-type GaAs layers: Effects of ion species and implant temperature . . . 206 (2003) 1008
Aitchison, J.S., see García-Blanco, S. . . . 206 (2003) 440
Aizawa, T., see Mitsuo, A. . . . 206 (2003) 366
Akamatsu, H., see Nishimura, Y. . . . 206 (2003) 696
Akedo, J., see Wang, Q. . . . 206 (2003) 118
Akedo, J., see Ogiso, H. . . . 206 (2003) 157
Aksenov, V.P., see Bayazitov, R.M. . . . 206 (2003) 984
Aktas, B., see Khaibullin, R.I. . . . 206 (2003) 277
Aktas, B., see Khaibullin, R.I. . . . 206 (2003) 1115
Al-Ajili, A., see Marchal, J. . . . 206 (2003) 462
Allen, C.W., see Mitsuishi, K. . . . 206 (2003) 109
Allen, L.P., see Insepov, Z. . . . 206 (2003) 846
Alves, E., R.C. da Silva, J.V. Pinto, T. Monteiro, B. Savoini, D. Cáceres, R. González and Y. Chen, Radiation-damage recovery in undoped and oxidized Li doped MgO crystals implanted with lithium ions . . . 206 (2003) 148
Alves, E., see Wendler, E. . . . 206 (2003) 1028
Alves, E., U. Wahl, M.R. Correia, S. Pereira, B. De Vries and A. Vantomme, Annealing behavior and lattice site location of Er implanted InGaN . . . 206 (2003) 1042
Alves, E., E. Rita, U. Wahl, J.G. Correia, T. Monteiro, J. Soares and C. Boemare, Lattice site location and optical activity of Er implanted ZnO . . . 206 (2003) 1047
Amaral, L., see Kling, A. . . . 206 (2003) 653
Amekura, H., N. Umeda, N. Okubo and N. Kishimoto, Ion-induced frequency shift of ~1100 cm^{-1} IR vibration in implanted SiO_2: Compaction versus bond-breaking . . . 206 (2003) 1101
Ando, M., see Nakamura, K. . . . 206 (2003) 798
Angelov, Ch., see Kaschieva, S. . . . 206 (2003) 452
Angelov, Ch., M. Takai, A. Kinomura, Y. Horino, A. Peeva and W. Skorupa, Ion beam induced epitaxial crystallization of silicon implanted with heavy ions . . . 206 (2003) 907
Anpo, M., see Yamashita, H. . . . 206 (2003) 889
Anpo, M., see Yamashita, H. . . . 206 (2003) 898
Antonova, L.Kh., see Bayazitov, R.M. . . . 206 (2003) 984

doi:10.1016/S0168-583X(03)01332-6

Anuntalabhochai, S., see Yu, L.D. 206 (2003) 586
Aoki, M., see Wang, A. 206 (2003) 219
Aoki, T., see Matsuo, J. 206 (2003) 838
Aoki, T., see Nakai, A. 206 (2003) 842
Aoki, T., J. Matsuo, G. Takaoka, N. Toyoda and I. Yamada, Defect characteristics by boron cluster ion implantation 206 (2003) 855
Aoki, T., J. Matsuo, G. Takaoka and I. Yamada, Cluster species and cluster size dependence of damage formation by cluster ion impact 206 (2003) 861
Aoyagi, Y., see Koguchi, Y. 206 (2003) 202
Apavatjrut, P., see Yu, L.D. 206 (2003) 586
Arai, N., see Tsuji, H. 206 (2003) 615
Arai, N., H. Tsuji, M. Motono, Y. Gotoh, K. Adachi, H. Kotaki and J. Ishikawa, Formation of silver nanoparticles in thin oxide layer on Si by negative-ion implantation 206 (2003) 629
Arakawa, K., K. Saitoh, H. Mori and K. Ono, Comparison among the formation processes of extended defects in Si under irradiation with low-energy H^+, He^+ ions and high-energy electrons 206 (2003) 76
Arakawa, K., see Ono, K. 206 (2003) 114
Araki, T., see Ikehata, T. 206 (2003) 772
Arora, S.K., see Kono, K. 206 (2003) 291
Aruga, T., see Nakazawa, T. 206 (2003) 166
Asai, K., see Koshimizu, M. 206 (2003) 57
Asai, K., see Umebayashi, T. 206 (2003) 264
Asanuma, T., see Matsutani, T. 206 (2003) 343
Asanuma, T., see Liu, C. 206 (2003) 348
Ashok, S., see Rangan, S. 206 (2003) 417
Assmann, W., see Mändl, S. 206 (2003) 668
Assmann, W., see Hammerl, C. 206 (2003) 1072
Aubert, P., see Jagielski, J. 206 (2003) 1097
Avalos, V., see Poirier, R. 206 (2003) 85
Avasthi, D.K., see Singh, N. 206 (2003) 1120
Azuma, K., see Nishimura, Y. 206 (2003) 696
Azuma, K., see Oka, Y. 206 (2003) 700
Azuma, Y., see Abe, H. 206 (2003) 224

Baba, K. and R. Hatada, Deposition of diamond-like carbon films on inner wall of sub-millimeter diameter steel tube by plasma source ion implantation 206 (2003) 704
Baba, K. and R. Hatada, Deposition of diamond-like carbon films by plasma source ion implantation with superposed pulse 206 (2003) 708
Baba, S., see Shibata, T. 206 (2003) 139
Baba, S., see Motohashi, Y. 206 (2003) 144
Bae, In.-T., M. Ishimaru, Y. Hirotsu, S. Matsumura and K.E. Sickafus, Ion-beam-induced amorphous structures in silicon carbide 206 (2003) 974
Baglin, J.E.E., see García-Blanco, S. 206 (2003) 440
Baibich, M.N., see Heck, C. 206 (2003) 601
Bakhtin, A.I., see Khaibullin, R.I. 206 (2003) 277
Baldo, P.M., see Rehn, L.E. 206 (2003) 490
Baldo, P.M., see Birtcher, R.C. 206 (2003) 851
Bandourko, V., N. Umeda, T. Suga, C.G. Lee, K. Kono, Y. Takeda and N. Kishimoto, Nanoparticles formation in insulators induced by Au^- and Au_2^- ion implantation 206 (2003) 606
Bandourko, V.V., see Umeda, N. 206 (2003) 657
Bandourko, V.V., see Suga, T. 206 (2003) 947
Barbour, J.C., see Johnson, C.M. 206 (2003) 1062
Barroso, J.J., see Ueda, M. 206 (2003) 760
Batalov, R.I., see Bayazitov, R.M. 206 (2003) 984
Baumann, H., see Markwitz, A. 206 (2003) 179
Bayazitov, R.M., I.B. Khaibullin, R.I. Batalov, R.M. Nurutdinov, L.Kh. Antonova, V.P. Aksenov and G.N. Mikhailova, Structure and photoluminescent properties of SiC layers on Si, synthesized by pulsed ion-beam treatment 206 (2003) 984

Bazarov, V.V., see Khaibullin, R.I. . . . 206 (2003) 277
Beauvy, M., see Trocellier, P. . . . 206 (2003) 1077
Belogorohov, A.S., see Gerasimenko, N.N. . . . 206 (2003) 644
Beloto, A.F., M.D. Silva, J.R. Senna, C. Kuranaga, N.F. Leite and M. Ueda, Photoluminescence and reflectance measurements on annealed porous silicon implanted with nitrogen by plasma immersion ion implantation (PIII) . . . 206 (2003) 677
Benyagoub, A., Kinetics of the crystalline to crystalline phase transformation induced in pure zirconia by swift heavy ion irradiation . . . 206 (2003) 132
Bernas, H., see Ruault, M.-O. . . . 206 (2003) 912
Berti, M., see De Salvador, D. . . . 206 (2003) 922
Bharuth-Ram, K., see Weyer, G. . . . 206 (2003) 90
Bharuth-Ram, K., U. Wahl and J.G. Correia, Lattice location of Fe in diamond . . . 206 (2003) 941
Bilek, M.M.M., see McKenzie, D.R. . . . 206 (2003) 741
Birtcher, R.C., see Mitsuishi, K. . . . 206 (2003) 109
Birtcher, R.C., see Ono, K. . . . 206 (2003) 114
Birtcher, R.C., see Nordlund, K. . . . 206 (2003) 189
Birtcher, R.C., see Donnelly, S.E. . . . 206 (2003) 422
Birtcher, R.C., see Rehn, L.E. . . . 206 (2003) 490
Birtcher, R.C., A.W. McCormick, P.M. Baldo, N. Toyoda, I. Yamada and J. Matsuo, Gold nanoparticles sputtered by single ions and clusters . . . 206 (2003) 851
Bisognin, G., see De Salvador, D. . . . 206 (2003) 922
Boemare, C., see Alves, E. . . . 206 (2003) 1047
Bohne, Y., see Hammerl, C. . . . 206 (2003) 1072
Bower, R.W., see Verda, R.D. . . . 206 (2003) 927
Bringa, E.M., see Papaléo, R.M. . . . 206 (2003) 7
Brown, I.G., see Yu, L.D. . . . 206 (2003) 586

Cáceres, D., see Alves, E. . . . 206 (2003) 148
Callegari, A.C., see Doyle, J.P. . . . 206 (2003) 467
Carnera, A., see De Salvador, D. . . . 206 (2003) 922
Carter, G., see Donnelly, S.E. . . . 206 (2003) 422
Chassé, T., H. Neumann and B. Rauschenbach, Ion beam assisted deposition of multi-layer X-ray mirrors for the extreme ultraviolet lithography . . . 206 (2003) 377
Chaudhari, P., see Doyle, J.P. . . . 206 (2003) 467
Chayahara, A., see Fukumi, K. . . . 206 (2003) 353
Chayahara, A., see Heck, C. . . . 206 (2003) 601
Chayahara, A., see Tojo, H. . . . 206 (2003) 717
Chayahara, A., see Lee, Y.-Y. . . . 206 (2003) 754
Chen, G., see Rangan, S. . . . 206 (2003) 417
Chen, H., see Shao, L. . . . 206 (2003) 413
Chen, J.Y., see Yang, P. . . . 206 (2003) 721
Chen, Y., see Alves, E. . . . 206 (2003) 148
Chen, Z.Q., see Abe, H. . . . 206 (2003) 224
Cheung, W.Y., see Gao, Y. . . . 206 (2003) 317
Chiang, S.L., see Liang, J.H. . . . 206 (2003) 932
Chiba, A., see Kitazawa, S.-i. . . . 206 (2003) 952
Chimi, Y., see Ono, F. . . . 206 (2003) 295
Choi, W.K., see Jeon, G.Y. . . . 206 (2003) 409
Choi, Y., S. Yamamoto, H. Saitoh, T. Sumita and H. Itoh, Influence of carbon-ion irradiation and hydrogen-plasma treatment on photocatalytic properties of titanium dioxide films . . . 206 (2003) 241
Chu, P.K., see Zhang, Q.Y. . . . 206 (2003) 357
Chu, P.K., see Tian, X.B. . . . 206 (2003) 673
Chu, P.K., see Li, L.H. . . . 206 (2003) 691
Chu, P.K., see Yang, P. . . . 206 (2003) 721
Chu, P.K., see Tang, D.L. . . . 206 (2003) 808
Chu, W.-K., see Shao, L. . . . 206 (2003) 413
Coindeau, S., see Jagielski, J. . . . 206 (2003) 1097

Collaborative Research Centre for Cluster Ion Beam Process Technology, see Yamada, I. 206 (2003) 820
Cooper, J.M., see García-Blanco, S. 206 (2003) 440
Correia, J.G., see Bharuth-Ram, K. 206 (2003) 941
Correia, J.G., see Alves, E. 206 (2003) 1047
Correia, M.R., see Alves, E. 206 (2003) 1042
Costantini, J.M., see Trocellier, P. 206 (2003) 1077
Cui, F.-Z., see Lee, I.-S. 206 (2003) 522
Cui, X.M., see Li, L.H. 206 (2003) 691

Dahmen, U., see Mitsuishi, K. 206 (2003) 109
Dallaqua, R.S., see Ueda, M. 206 (2003) 760
Dannefaer, S., see Poirier, R. 206 (2003) 85
da Silva, R.C., see Alves, E. 206 (2003) 148
Degi, K., see Yamaguchi, H. 206 (2003) 561
Degi, K., see Morishita, T. 206 (2003) 565
De La Rue, R.M., see García-Blanco, S. 206 (2003) 440
de M. Azevedo, G., C.J. Glover, K.M. Yu, G.J. Foran and M.C. Ridgway, Direct observation of structural relaxation in amorphous compound semiconductors 206 (2003) 1024
Demenkov, P.V., see Plaksin, O.A. 206 (2003) 1083
De Salvador, D., E. Napolitani, S. Mirabella, F. Giannazzo, V. Raineri, G. Bisognin, M. Berti, A. Carnera, A.V. Drigo, A. Terrasi and F. Priolo, New insight on the interaction and diffusion properties of ion beam injected self-interstitials in crystalline silicon 206 (2003) 922
Deschanels, X., see Trocellier, P. 206 (2003) 1077
De Vries, B., see Alves, E. 206 (2003) 1042
Dietrich, M., see Weyer, G. 206 (2003) 90
Dizard, Z.L., see Kasukabe, Y. 206 (2003) 390
Djamanbalin, K.K., see Gerasimenko, N.N. 206 (2003) 299
Djamanbalin, K.K., see Gerasimenko, N.N. 206 (2003) 644
Djurabekova, F.G., B.E. Umirzakov, F.F. Umarov and Y. Miyagawa, Effect of high-dose low-energy reactive-ion implantation on cold cathode properties 206 (2003) 194
Dmitriev, S.N., see Kaschieva, S. 206 (2003) 452
Doak, D., see Marchal, J. 206 (2003) 462
Donnelly, S.E., see Nordlund, K. 206 (2003) 189
Donnelly, S.E., V.M. Vishnyakov, G. Carter, J. Terry, L.I. Haworth, P. Sermanni and R.C. Birtcher, The use of cavities for gettering in silicon microelectronic devices 206 (2003) 422
Doyle, J.P., P. Chaudhari, J.L. Lacey, E.A. Galligan, S.C. Lien, A.C. Callegari, N.D. Lang, M. Lu, Y. Nakagawa, H. Nakano, N. Okazaki, S. Odahara, Y. Katoh, Y. Saitoh, K. Sakaib, H. Satoh and Y. Shiota, Ion beam alignment for liquid crystal display fabrication 206 (2003) 467
Drigo, A.V., see De Salvador, D. 206 (2003) 922
Dytlewski, N., see Johnson, P.B. 206 (2003) 1056

Echigo, T., see Kitahara, N. 206 (2003) 999
Eguchi, H., see Sadoh, T. 206 (2003) 478
Eichhorn, F., see Kögler, R. 206 (2003) 989
Elliman, R.G., M.J. Lederer, N. Smith and B. Luther-Davies, The fabrication and properties of silicon-nanocrystal-based devices and structures produced by ion implantation – The search for gain 206 (2003) 427
Enders, B., see Lee, Y.-Y. 206 (2003) 754
Endo, H., see Sakudo, N. 206 (2003) 687
Enomoto, Y. and M. Sawa, Simulation study on nanocluster growth by ion beam synthesis 206 (2003) 596
Ensinger, W., O. Lensch, F. Sittner, J. Knecht, K. Volz, T. Matsutani and M. Kiuchi, Argon versus nitrogen ion beam assisted deposition of amorphous carbon and carbon–nitrogen films on aluminum for protection against aqueous corrosion 206 (2003) 334
Ensinger, W., see Lee, Y.-Y. 206 (2003) 754
Eriksson, J., see Milanez Silva, C. 206 (2003) 486
Eryu, O., see Abe, K. 206 (2003) 960
Eryu, O., K. Abe, K. Nakashima and H. Harima, Kinetics of solid phase regrowth of self-ion-implanted amorphous SiC during low temperature furnace annealing 206 (2003) 969

Evans, P., see Yu, L.D. 206 (2003) 586
Ewing, R.C., see Zhu, S. 206 (2003) 1092

Fanciulli, M., see Weyer, G. 206 (2003) 90
Faulkner, R.G., see Kishimoto, N. 206 (2003) 634
Feng, T., Q. Li, J. Xu, X. Wang, X. Liu and S. Zou, Nodose carbon nanotubes and its field emission characteristics 206 (2003) 198
Fichtner, P.F.P., see Kling, A. 206 (2003) 653
Fichtner, P.P., see Milanez Silva, C. 206 (2003) 486
Flauta, R., see Wada, M. 206 (2003) 557
Földvári, I., see Kling, A. 206 (2003) 653
Foran, G.J., see de M. Azevedo, G. 206 (2003) 1024
Fortuna, F., see Ruault, M.-O. 206 (2003) 912
Frantz, J., K. Nordlund and J. Keinonen, Burrowing of cobalt nanoclusters in copper 206 (2003) 66
Fröjdh, Ch., see Marchal, J. 206 (2003) 462
Fu, R.K.Y., see Tang, D.L. 206 (2003) 808
Fujino, Y., see Kasukabe, Y. 206 (2003) 390
Fujita, J., M. Ishida, T. Ichihashi, Y. Ochiai, T. Kaito and S. Matsui, Growth of three-dimensional nanostructures using FIB-CVD and its mechanical properties 206 (2003) 472
Fujita, K., see Xu, G.C. 206 (2003) 362
Fujiwara, E., see Oka, Y. 206 (2003) 700
Fujiwara, T., see Mukaigawa, S. 206 (2003) 777
Fujiwara, T., see Takaki, K. 206 (2003) 794
Fujiwara, Y., N. Toyoda, K. Mochiji, T. Mitamura and I. Yamada, Reduction of surface roughness by Ta_2O_5 film formation with O_2 cluster ion assisted deposition 206 (2003) 870
Fujiwara, Y., see Toyoda, N. 206 (2003) 875
Fukudome, T., A. Kaminaka, H. Isshiki, R. Saito, S. Yugo and T. Kimura, Optical characterization of Er-implanted ZnO films formed by sol–gel method 206 (2003) 287
Fukui, K., see Kitamura, S. 206 (2003) 548
Fukumi, K., A. Chayahara, H. Kageyama, A. Kinomura, Y. Mokuno, N. Kitamura, K. Kadono, Y. Horino and J. Nishii, Sequential implantation of halogen and copper ions in silica glass 206 (2003) 353
Funahashi, R., see Heck, C. 206 (2003) 601
Funayama, T., see Wada, S. 206 (2003) 553
Furuya, K., see Mitsuishi, K. 206 (2003) 109

Gaiduk, P.I., see Wesch, W. 206 (2003) 1018
Galligan, E.A., see Doyle, J.P. 206 (2003) 467
Gamo, K., see Yuba, Y. 206 (2003) 648
Gamo, K., see Itou, M. 206 (2003) 1013
Ganeev, R.A., see Stepanov, A.L. 206 (2003) 624
Gao, F., see Weber, W.J. 206 (2003) 1
Gao, Y., S.P. Wong, W.Y. Cheung, G. Shao and K.P. Homewood, Characterization and light emission properties of β-$FeSi_2$ precipitates in Si synthesized by metal vapor vacuum arc ion implantation 206 (2003) 317
García-Blanco, S., A.J. Kellock, J.E.E. Baglin, A. Glidle, J.M. Cooper, J.S. Aitchison and R.M. De La Rue, Fabrication of optical waveguides by 2 MeV Ar^+ irradiation of germanium-doped flame-hydrolysis deposited silica 206 (2003) 440
Gärtner, K., see Wesch, W. 206 (2003) 1018
Gärtner, K., see Wendler, E. 206 (2003) 1028
Gejo, T., see Kanda, K. 206 (2003) 880
Gerasimenko, N.N., M.N. Pavluchenko, V.D. Levchenko, K.K. Djamanbalin, V.Yu. Troitskiy and A.M. Skobochkin, Fractal, wavelet and Fourier analysis for investigation of nanoscale $CoSi_2$ structures in Si produced by ion synthesis 206 (2003) 299
Gerasimenko, N.N., Yu.N. Parhomenko, V.Yu. Troitskiy, A.V. Irzhak, M.N. Pavluchenko, K.K. Djamanbalin and A.S. Belogorohov, Quantum-dimensional structures produced by ion implantation 206 (2003) 644
Gerlach, J.W., see Mändl, S. 206 (2003) 668
Giannazzo, F., see De Salvador, D. 206 (2003) 922
Glidle, A., see García-Blanco, S. 206 (2003) 440

Glover, C.J., see de M. Azevedo, G. 206 (2003) 1024
Golanski, A., J.P. Stoquert, P. Kern, F. Piazza and S. Schulze, Impact of energy density and stress fields on the nucleation dynamics of plasma deposited a-C:H films 206 (2003) 731
Golombeck, M.-A., S. Heise, K. Schloesser, B. Schuessler and H. Schweickert, Intravascular brachytherapy with radioactive stents produced by ion implantation 206 (2003) 495
Gomes, G.F., see Ueda, M. 206 (2003) 749
González, R., see Alves, E. 206 (2003) 148
Gosset, D., see Trocellier, P. 206 (2003) 1077
Gotoh, Y., see Tsuji, H. 206 (2003) 249
Gotoh, Y., see Tsuji, H. 206 (2003) 507
Gotoh, Y., see Tsuji, H. 206 (2003) 615
Gotoh, Y., see Arai, N. 206 (2003) 629
Grismanovs, V., see Nakazawa, T. 206 (2003) 166
Grynszpan, R., see Trocellier, P. 206 (2003) 1077
Gunnlaugsson, H.P., see Weyer, G. 206 (2003) 90
Gwilliam, R., see Marchal, J. 206 (2003) 462
Gwilliam, R., see Ahmed, S. 206 (2003) 1003
Gwilliam, R., see Ahmed, S. 206 (2003) 1008
Gwilliam, R.M., see Lourenço, M.A. 206 (2003) 436

Häberlen, M., J.K.N. Lindner and B. Stritzker, Creation of internal point defect drains in silicon by carbon implantation 206 (2003) 916
Hamatani, Y., see Ono, F. 206 (2003) 295
Hammerl, C., Y. Bohne, W. Assmann, K. Helming and B. Rauschenbach, Formation of buried oxide layers in titanium by high-fluence oxygen ion implantation 206 (2003) 1072
Haneda, H., see Sakaguchi, I. 206 (2003) 153
Haneda, H., see Hishita, S. 206 (2003) 171
Harada, M., see Yamashita, H. 206 (2003) 889
Harada, N. and H. Takai, Formation of β-$FeSi_2$ thin films by partially ionized vapor deposition 206 (2003) 308
Haraguchi, M., H. Yamamoto, K. Yamaguchi, T. Nakanoya, T. Saito, M. Sasase and K. Hojou, Effect of surface treatment of Si substrate on the crystal structure of $FeSi_2$ thin film formed by ion beam sputter deposition method 206 (2003) 313
Haraguchi, M., see Saito, T. 206 (2003) 321
Harima, H., see Eryu, O. 206 (2003) 969
Harjo, S., see Shibata, T. 206 (2003) 139
Harjo, S., see Motohashi, Y. 206 (2003) 144
Haruyama, Y., see Kanda, K. 206 (2003) 880
Hase, M., see Kitajima, M. 206 (2003) 99
Hase, Y., see Yamaguchi, H. 206 (2003) 561
Hase, Y., see Morishita, T. 206 (2003) 565
Hase, Y., see Ishii, K. 206 (2003) 570
Hase, Y., see Okamura, M. 206 (2003) 574
Hase, Y., see Maekawa, M. 206 (2003) 579
Hatada, R., see Baba, K. 206 (2003) 704
Hatada, R., see Baba, K. 206 (2003) 708
Haworth, L.I., see Donnelly, S.E. 206 (2003) 422
Hayashi, K., H. Konno, T. Oseki, H. Kojima and T. Kanayama, Comparison of methods to measure the rate of neutral free radical production by photo-deionization of negative ion beams 206 (2003) 403
Hayashi, N., T. Moriwaki, I. Sakamoto, T. Toriyama and H. Wakabayashi, TMR effects of sputtered Fe–Al–O granular films after irradiation by high energy ions 206 (2003) 1066
Hazama, S., see Yuba, Y. 206 (2003) 648
Heck, C., A. Chayahara, Y. Horino, R. Funahashi, R.M.N. Miranda and M.N. Baibich, Resistivity of nanostructured Fe–Cr films 206 (2003) 601
Heck, C., see Lee, Y.-Y. 206 (2003) 754
Heera, V., see Kögler, R. 206 (2003) 989
Heise, S., see Golombeck, M.-A. 206 (2003) 495
Helming, K., see Hammerl, C. 206 (2003) 1072

Hibino, Y., see Xu, G.C. 206 (2003) 330
Hibino, Y., see Xu, G.C. 206 (2003) 362
Hida, A., see Koguchi, Y. 206 (2003) 202
Hidaka, T., see Tojo, H. 206 (2003) 717
Higashi, Y., see Wang, A. 206 (2003) 219
Higuchi, T., K. Yasuda, K. Tanaka, K. Shiiyama and C. Kinoshita, Ion-beam induced defect formation in α-alumina with applied electric field 206 (2003) 103
Hijino, M., see Tojo, H. 206 (2003) 717
Hiller, J., see Rehn, L.E. 206 (2003) 490
Hirao, T., see Mori, H. 206 (2003) 31
Hirao, T., see Laird, J.S. 206 (2003) 36
Hirao, T., see Onoda, S. 206 (2003) 444
Hirao, T., H. Mori, J.S. Laird, S. Onoda, H. Abe, T. Wakasa and H. Itoh, Study of single-event current pulses induced in SOI diodes by collimated swift heavy-ions micro-beams 206 (2003) 457
Hirao, T., see Ohshima, T. 206 (2003) 979
Hirata, K., Y. Saitoh, K. Narumi and Y. Kobayashi, Effect of external bias potential on secondary charged emissions from polycarbonate by C_1^+ and C_8^+ bombardments 206 (2003) 47
Hirotsu, Y., see Bae, In.-T. 206 (2003) 974
Hirotsu, Y., see Ishimaru, M. 206 (2003) 994
Hishita, S., see Sakaguchi, I. 206 (2003) 153
Hishita, S., H. Haneda, S.S. Kim and J.H. Moon, Recrystallization of ion-beam amorphized BSCC thin films 206 (2003) 171
Hitomi, N., see Wang, A. 206 (2003) 219
Hitomi, T., see Nakamura, T. 206 (2003) 956
Hobler, G. and G. Otto, Amorphous pocket model for silicon based on molecular dynamics simulations 206 (2003) 81
Hogg, S.M., see Pipeleers, B. 206 (2003) 95
Hojou, K., see Haraguchi, M. 206 (2003) 313
Hojou, K., see Saito, T. 206 (2003) 321
Homewood, K.P., see Gao, Y. 206 (2003) 317
Homewood, K.P., see Lourenço, M.A. 206 (2003) 436
Honda, S., see Purwanto, S. 206 (2003) 326
Horch, H.H., see Mändl, S. 206 (2003) 517
Horibe, H., see Tanaka, T. 206 (2003) 817
Horino, Y., see Fukumi, K. 206 (2003) 353
Horino, Y., see Heck, C. 206 (2003) 601
Horino, Y., see Tojo, H. 206 (2003) 717
Horino, Y., see Lee, Y.-Y. 206 (2003) 754
Horino, Y., see Angelov, Ch. 206 (2003) 907
Hoshiya, T., see Shibata, T. 206 (2003) 139
Hoshiya, T., see Motohashi, Y. 206 (2003) 144
Hu, L., Z.F. Li, W.S. Lai and B.X. Liu, Physical origin of ion mixing induced amorphization and associated asymmetric growth in the binary metal systems 206 (2003) 127
Huang, H.C., see Xu, Q. 206 (2003) 123
Huang, N., see Yang, P. 206 (2003) 721

Ichihashi, T., see Fujita, J. 206 (2003) 472
Ichikawa, T., see Koizumi, H. 206 (2003) 1124
Ikeda, T., see Kitagawa, T. 206 (2003) 884
Ikeda, T., see Kurooka, S. 206 (2003) 1088
Ikeguchi, R., see Tsuji, H. 206 (2003) 507
Ikehata, T., K. Shioya, T. Araki, N.Y. Sato, H. Mase and K. Yukimura, Sheath formation and ion flux distribution inside the trench in plasma-based ion implantation 206 (2003) 772
Ikehata, T., K. Shimatsu, N.Y. Sato and H. Mase, Positive pulse bias method in plasma-based ion implantation 206 (2003) 782
Ikehata, T., see Ma, X.X. 206 (2003) 813
Ikenaga, N., see Sakudo, N. 206 (2003) 687
Ikeyama, M., see Miyagawa, Y. 206 (2003) 767
Im, S., see Jeon, G.Y. 206 (2003) 409
Im, S., see Park, C.H. 206 (2003) 432

Imaizumi, M., see Sumita, T. . . . 206 (2003) 448
Imamura, M., see Saito, T. . . . 206 (2003) 321
Imamura, Y., see Saito, Y. . . . 206 (2003) 272
Inoue, M., see Kitamura, S. . . . 206 (2003) 548
Insepov, Z., L.P. Allen, C. Santeufemio, K.S. Jones and I. Yamada, Crater formation and sputtering by cluster impacts . . . 206 (2003) 846
Irzhak, A.V., see Gerasimenko, N.N. . . . 206 (2003) 644
Ishida, M., see Fujita, J. . . . 206 (2003) 472
Ishihara, M., see Shibata, T. . . . 206 (2003) 139
Ishihara, M., see Motohashi, Y. . . . 206 (2003) 144
Ishii, K., Y. Yamada, Y. Hase, N. Shikazono and A. Tanaka, RAPD analysis of mutants obtained by ion beam irradiation to hinoki cypress shoot primordia . . . 206 (2003) 570
Ishikawa, H., see Wang, Q. . . . 206 (2003) 118
Ishikawa, J., see Tsuji, H. . . . 206 (2003) 249
Ishikawa, J., see Tsuji, H. . . . 206 (2003) 507
Ishikawa, J., see Tsuji, H. . . . 206 (2003) 615
Ishikawa, J., see Arai, N. . . . 206 (2003) 629
Ishikawa, N., see Ono, F. . . . 206 (2003) 295
Ishimaru, M., see Bae, In.-T. . . . 206 (2003) 974
Ishimaru, M., M. Naito, Y. Hirotsu and K.E. Sickafus, Amorphous structures of silicon carbonitride formed by high-dose nitrogen ion implantation into silicon carbide . . . 206 (2003) 994
Ishioka, K., see Kitajima, M. . . . 206 (2003) 99
Ishioka, N.S., see Watanabe, S. . . . 206 (2003) 399
Isogawa, S., see Tojo, H. . . . 206 (2003) 717
Isoya, J., T. Ohshima, A. Ohi, N. Morishita and H. Itoh, ESR characterization of activation of implanted phosphorus ions in silicon carbide . . . 206 (2003) 965
Isshiki, H., see Fukudome, T. . . . 206 (2003) 287
Isshiki, M., see Lim, J.-W. . . . 206 (2003) 371
Ito, A., see Lee, I.-S. . . . 206 (2003) 522
Ito, N., see Wada, S. . . . 206 (2003) 553
Ito, Y., see Takahiro, K. . . . 206 (2003) 639
Itoh, H., see Mori, H. . . . 206 (2003) 31
Itoh, H., see Laird, J.S. . . . 206 (2003) 36
Itoh, H., see Abe, H. . . . 206 (2003) 224
Itoh, H., see Choi, Y. . . . 206 (2003) 241
Itoh, H., see Yamaki, T. . . . 206 (2003) 254
Itoh, H., see Onoda, S. . . . 206 (2003) 444
Itoh, H., see Sumita, T. . . . 206 (2003) 448
Itoh, H., see Hirao, T. . . . 206 (2003) 457
Itoh, H., see Isoya, J. . . . 206 (2003) 965
Itoh, H., see Ohshima, T. . . . 206 (2003) 979
Itoh, H., see Nakanishi, Y. . . . 206 (2003) 1033
Itoh, M., see Matsunami, N. . . . 206 (2003) 282
Itou, M., M. Kasai, T. Kimura, J. Yanagisawa, F. Wakaya, Y. Yuba and K. Gamo, Maskless Mn implantation in GaAs using focused Mn ion beam . . . 206 (2003) 1013
Iura, S., see Tojo, H. . . . 206 (2003) 717
Iwaki, M., see Kobayashi, T. . . . 206 (2003) 184
Iwaki, M., see Takahiro, K. . . . 206 (2003) 206
Iwaki, M., see Nakao, A. . . . 206 (2003) 211
Iwaki, M., see Xu, G.C. . . . 206 (2003) 330
Iwaki, M., see Yokoyama, Y. . . . 206 (2003) 512
Iwaki, M., see Yotoriyama, T. . . . 206 (2003) 527
Iwaki, M., see Kurotobi, K. . . . 206 (2003) 532
Iwaki, M., see Suzuki, Y. . . . 206 (2003) 538
Iwaki, M., see Okuyama, Y. . . . 206 (2003) 543
Iwaki, M., see Watanabe, H. . . . 206 (2003) 1106
Iwaki, M., see Kobayashi, T. . . . 206 (2003) 1110

Iwase, A., see Ono, F. 206 (2003) 295
Izukawa, M., see Tsuji, H. 206 (2003) 507

Jagielski, J., see Piatkowska, A. 206 (2003) 1052
Jagielski, J., A. Piatkowska, Z. Librant, P. Aubert, C. Legrand-Buscema and S. Coindeau, Friction properties of ion implanted Al_2O_3 ceramic 206 (2003) 1097
Jeon, G.Y., J.S. Kim, C.N. Whang, S. Im, J.-H. Song, J.H. Song, W.K. Choi and H.K. Kim, Formation and characterizations of ultra-shallow p^+–n junctions using $B_{10}H_{14}$ ion implantation 206 (2003) 409
Jiang, W., see Weber, W.J. 206 (2003) 1
Jiang, W., see Thevuthasan, S. 206 (2003) 162
Jiang, W., W.J. Weber and C.M. Wang, Ion-beam-irradiation induced defects in gallium nitride 206 (2003) 1037
Johnson, C.M., F.D. Wall and J.C. Barbour, Using ion implantation to study localized corrosion of Al 206 (2003) 1062
Johnson, P.B., V.J. Kennedy, A. Markwitz, C.R. Varoy, N. Dytlewski and K.T. Short, Uptake of light elements of nanoporous layers formed by helium ion implantation 206 (2003) 1056
Jones, K.S., see Insepov, Z. 206 (2003) 846

Kadono, K., see Fukumi, K. 206 (2003) 353
Kageyama, H., see Fukumi, K. 206 (2003) 353
Kaito, T., see Fujita, J. 206 (2003) 472
Kakinoki, R., see Tsuji, H. 206 (2003) 507
Kakiuchi, H. and T. Terai, Preferential sputtering from the surface of amorphous carbon nitride (a-C:N) thin films upon ion implantation 206 (2003) 27
Kakiuchi, H. and T. Terai, Effects of ion implantation on various properties of amorphous carbon nitride (a-C:N) thin films 206 (2003) 237
Kamarou, A., see Wesch, W. 206 (2003) 1018
Kamarou, A., see Wendler, E. 206 (2003) 1028
Kambara, T., see Ono, F. 206 (2003) 295
Kaminaka, A., see Fukudome, T. 206 (2003) 287
Kamio, M., see Suzuki, Y. 206 (2003) 538
Kamiya, T., see Ohshima, T. 206 (2003) 979
Kanayama, T., see Hayashi, K. 206 (2003) 403
Kanda, K., Y. Shimizugawa, Y. Haruyama, I. Yamada, S. Matsui, T. Kitagawa, H. Tsubakino and T. Gejo, NEXAFS study on substrate temperature dependence of DLC films formed by Ar cluster ion beam assisted deposition 206 (2003) 880
Kanda, K., see Kitagawa, T. 206 (2003) 884
Kanno, S., see Mukaigawa, S. 206 (2003) 777
Kasai, H., see Tojo, H. 206 (2003) 717
Kasai, M., see Itou, M. 206 (2003) 1013
Kaschieva, S., S.N. Dmitriev and Ch. Angelov, Electron and γ-irradiation of ion implanted MOS structures with different oxide thickness 206 (2003) 452
Kasukabe, Y., Z.L. Dizard, Y. Fujino, H. Tani, M. Osaka, Y. Yamada and H. Abe, In situ observation of formation processes of titanium compound thin films due to ion implantation in a transmission electron microscope 206 (2003) 390
Kasuya, T., see Yokota, K. 206 (2003) 386
Kasuya, T., see Wada, M. 206 (2003) 557
Katano, Y., see Nakazawa, T. 206 (2003) 166
Katoh, Y., see Doyle, J.P. 206 (2003) 467
Kawakami, H., see Okuyama, Y. 206 (2003) 543
Kawasuso, A., see Yamaki, T. 206 (2003) 254
Kawatsura, K., see Ookawa, R. 206 (2003) 175
Kawatsura, K., see Takahiro, K. 206 (2003) 206
Kawatsura, K., see Takahiro, K. 206 (2003) 639
Keinonen, J., see Pomoell, J. 206 (2003) 18
Keinonen, J., see Peltola, J. 206 (2003) 61
Keinonen, J., see Frantz, J. 206 (2003) 66
Keinonen, J., see Nordlund, K. 206 (2003) 189
Kellock, A.J., see García-Blanco, S. 206 (2003) 440

Kenjo, A., see Murakami, Y. . . . 206 (2003) 304
Kenjo, A., see Sadoh, T. . . . 206 (2003) 478
Kennedy, V.J., see Markwitz, A. . . . 206 (2003) 179
Kennedy, V.J., see Johnson, P.B. . . . 206 (2003) 1056
Kern, P., see Golanski, A. . . . 206 (2003) 731
Kestel, B.J., see Rehn, L.E. . . . 206 (2003) 490
Khaibullin, I.B., see Khaibullin, R.I. . . . 206 (2003) 277
Khaibullin, I.B., see Bayazitov, R.M. . . . 206 (2003) 984
Khaibullin, R.I., O.N. Lopatin, F.G. Vagizov, V.V. Bazarov, A.I. Bakhtin, I.B. Khaibullin and B. Aktas, Coloration of natural beryl by iron ion implantation . . . 206 (2003) 277
Khaibullin, R.I., B.Z. Rameev, V.N. Popok, E.P. Zheglov, A.V. Kondyurin, V.A. Zhikharev and B. Aktas, An influence of the viscosity of polymer substrate on ion beam synthesis of iron granular films . . . 206 (2003) 1115
Kido, H., see Murakami, Y. . . . 206 (2003) 304
Kiguchi, K., see Tu, Z.-L. . . . 206 (2003) 591
Kim, H.K., see Jeon, G.Y. . . . 206 (2003) 409
Kim, J.S., see Jeon, G.Y. . . . 206 (2003) 409
Kim, S.S., see Hishita, S. . . . 206 (2003) 171
Kim, T.G., see Park, C.H. . . . 206 (2003) 432
Kim, Y.T., see Nakanishi, Y. . . . 206 (2003) 1033
Kimura, T., see Fukudome, T. . . . 206 (2003) 287
Kimura, T., see Itou, M. . . . 206 (2003) 1013
Kinomura, A., see Fukumi, K. . . . 206 (2003) 353
Kinomura, A., see Angelov, Ch. . . . 206 (2003) 907
Kinoshita, C., see Higuchi, T. . . . 206 (2003) 103
Kirkpatrick, A., Gas cluster ion beam applications and equipment . . . 206 (2003) 830
Kishimoto, N., see Kono, K. . . . 206 (2003) 291
Kishimoto, N., see Bandourko, V. . . . 206 (2003) 606
Kishimoto, N., see Okubo, N. . . . 206 (2003) 610
Kishimoto, N., see Takeda, Y. . . . 206 (2003) 620
Kishimoto, N., Y. Takeda, N. Umeda, N. Okubo and R.G. Faulkner, Ion-induced metal nanoparticles in insulators for nonlinear optical property . . . 206 (2003) 634
Kishimoto, N., see Umeda, N. . . . 206 (2003) 657
Kishimoto, N., see Suga, T. . . . 206 (2003) 947
Kishimoto, N., see Plaksin, O.A. . . . 206 (2003) 1083
Kishimoto, N., see Amekura, H. . . . 206 (2003) 1101
Kitagawa, T., see Kanda, K. . . . 206 (2003) 880
Kitagawa, T., K. Miyauchi, N. Toyoda, K. Kanda, T. Ikeda, H. Tsubakino, J. Matsuo, S. Matsui and I. Yamada, Influence of residual Ar^+ in Ar cluster ion beam for DLC film formation . . . 206 (2003) 884
Kitagawa, T., see Miyauchi, K. . . . 206 (2003) 893
Kitahara, A., see Saito, Y. . . . 206 (2003) 272
Kitahara, N., T. Echigo, T. Otani and Y. Yamamoto, Formation of SiGe alloys using ion beam mixing followed by ion beam induced epitaxial crystallization . . . 206 (2003) 999
Kitajima, M., M. Hase, K. Ishioka and K. Ushida, Application of time-domain vibrational spectroscopy to the study of defects in ion-implanted materials . . . 206 (2003) 99
Kitamura, N., see Fukumi, K. . . . 206 (2003) 353
Kitamura, S., M. Inoue, N. Ohmido, K. Fukui and A. Tanaka, Chromosomal rearrangements in interspecific hybrids between *Nicotiana gossei* Domin and *N. tabacum* L., obtained by crossing with pollen exposed to helium ion beams or gamma-rays . . . 206 (2003) 548
Kitazawa, S.-i., T.Y.S. Panca Putra, S. Sakai, K. Narumi, H. Naramoto, S. Yamamoto and A. Chiba, Laser detection of surface acoustic waves as a method of measuring an Ar ion beam modification of carbon thin film 206 (2003) 952
Kiuchi, M., see Ensinger, W. . . . 206 (2003) 334
Kiuchi, M., see Matsutani, T. . . . 206 (2003) 343
Kiuchi, M., see Liu, C. . . . 206 (2003) 348
Klaumünzer, S., see Wesch, W. . . . 206 (2003) 1018
Kling, A., J.C. Soares, P.F.P. Fichtner, L. Amaral, F. Zawislak, I. Földvári and Á. Péter, Creation of noble metal nanoclusters in bismuth tellurite . . . 206 (2003) 653
Knecht, J., see Ensinger, W. . . . 206 (2003) 334

Kobayashi, T., see Shibata, T. . . . 206 (2003) 139
Kobayashi, T., see Motohashi, Y. . . . 206 (2003) 144
Kobayashi, T., M. Iwaki, T. Ubagai and K. Terashima, Formation of carbon needles from fluoropolymer by ion irradiation followed by defluorination . . . 206 (2003) 184
Kobayashi, T., see Yokoyama, Y. . . . 206 (2003) 512
Kobayashi, T., A. Nakao and M. Iwaki, Wear properties of tungsten-implanted polyimide . . . 206 (2003) 1110
Kobayashi, Y., see Hirata, K. . . . 206 (2003) 47
Kobayashi, Y., see Wada, S. . . . 206 (2003) 553
Kobayashi, Y., see Tu, Z.-L. . . . 206 (2003) 591
Kobayashi, Y., see Koizumi, H. . . . 206 (2003) 1124
Koegler, R., see Peeva, A. . . . 206 (2003) 71
Koga, Y., see Watanabe, T. . . . 206 (2003) 726
Kogi, O., see Abe, K. . . . 206 (2003) 960
Kögler, R., F. Eichhorn, A. Mücklich, H. Reuther, V. Heera, W. Skorupa and J.K.N. Lindner, SiC precipitates formed in Si by simultaneous dual beam implantation of C^+ and Si^+ ions . . . 206 (2003) 989
Koguchi, Y., T. Meguro, A. Hida, H. Takai, K. Maeda, Y. Yamamoto and Y. Aoyagi, Modification of highly oriented pyrolytic graphite (HOPG) surfaces with highly charged ion (HCI) irradiation . . . 206 (2003) 202
Kohata, M., see Yukimura, K. . . . 206 (2003) 745
Koike, M., see Purwanto, S. . . . 206 (2003) 326
Koizumi, H., T. Ichikawa, M. Taguchi, Y. Kobayashi and H. Namba, Chemical effects of heavy ion beams on organic materials . . . 206 (2003) 1124
Koizumi, Y., see Mori, H. . . . 206 (2003) 31
Koizumi, Y., see Onoda, S. . . . 206 (2003) 444
Kojima, H., see Hayashi, K. . . . 206 (2003) 403
Komatsu, S., see Ono, F. . . . 206 (2003) 295
Kondyurin, A.V., see Khaibullin, R.I. . . . 206 (2003) 1115
Konno, H., see Hayashi, K. . . . 206 (2003) 403
Kono, K., S.K. Arora and N. Kishimoto, Modification in optical properties of negative Cu ion implanted ZnO 206 (2003) 291
Kono, K., see Bandourko, V. . . . 206 (2003) 606
Kono, K., see Suga, T. . . . 206 (2003) 947
Kopcewicz, M., see Piatkowska, A. . . . 206 (2003) 1052
Koshimizu, M., K. Shibuya, K. Asai and H. Shibata, Observation of local heating in an ion track by measuring the ion-induced luminescence spectrum . . . 206 (2003) 57
Kotaki, H., see Tsuji, H. . . . 206 (2003) 615
Kotaki, H., see Arai, N. . . . 206 (2003) 629
Krasheninnikov, A.V., see Pomoell, J. . . . 206 (2003) 18
Krause, D., see Mändl, S. . . . 206 (2003) 517
Kuji, T., see Takeuchi, M. . . . 206 (2003) 259
Kumagai, M., see Yukimura, K. . . . 206 (2003) 745
Kumagai, M., see Takaki, K. . . . 206 (2003) 794
Kuranaga, C., see Beloto, A.F. . . . 206 (2003) 677
Kurooka, S., T. Ikeda and A. Tanaka, Improvement of the adhesion of cubic boron nitride films by adding miscellaneous elements . . . 206 (2003) 1088
Kurotobi, K., see Xu, G.C. . . . 206 (2003) 330
Kurotobi, K., Y. Suzuki, H. Nakajima, H. Suzuki and M. Iwaki, Platelet adhesion and plasma protein adsorption control of collagen surfaces by He^+ ion implantation . . . 206 (2003) 532
Kwok, S.C.H., see Yang, P. . . . 206 (2003) 721

Lacey, J.L., see Doyle, J.P. . . . 206 (2003) 467
Lai, W.S., see Hu, L. . . . 206 (2003) 127
Laird, J.S., see Mori, H. . . . 206 (2003) 31
Laird, J.S., T. Hirao, S. Onoda, H. Mori and H. Itoh, TCAD modeling of single MeV ion induced charge collection processes in Si devices . . . 206 (2003) 36
Laird, J.S., see Onoda, S. . . . 206 (2003) 444
Laird, J.S., see Hirao, T. . . . 206 (2003) 457
Laird, J.S., see Ohshima, T. . . . 206 (2003) 979
Lang, N.D., see Doyle, J.P. . . . 206 (2003) 467

Leal, R., see Papaléo, R.M. . . . 206 (2003) 7
Lederer, M.J., see Elliman, R.G. . . . 206 (2003) 427
Lee, C.G., see Bandourko, V. . . . 206 (2003) 606
Lee, C.G., see Suga, T. . . . 206 (2003) 947
Lee, G.H., see Lee, I.-S. . . . 206 (2003) 522
Lee, I.-S., C.-N. Whang, G.H. Lee, F.-Z. Cui and A. Ito, Effects of ion beam assist on the formation of calcium phosphate film . . . 206 (2003) 522
Lee, J.W., see Yoshida, M. . . . 206 (2003) 712
Lee, J.Y., see Park, C.H. . . . 206 (2003) 432
Lee, K.K., see Ohshima, T. . . . 206 (2003) 979
Lee, Y.-Y., C. Heck, A. Chayahara, Y. Horino, W. Ensinger and B. Enders, Electrochemical porosity determination of thin protective films on iron base materials . . . 206 (2003) 754
Legrand-Buscema, C., see Jagielski, J. . . . 206 (2003) 1097
Leite, N.F., see Beloto, A.F. . . . 206 (2003) 677
Leng, Y.X., see Yang, P. . . . 206 (2003) 721
Lensch, O., see Ensinger, W. . . . 206 (2003) 334
Levchenko, V.D., see Gerasimenko, N.N. . . . 206 (2003) 299
Li, L.H., X.B. Tian, P.K. Chu, Y.H. Zhang, X.M. Cui and H.Q. Zhang, Growth and nucleation of diamond-like carbon (DLC) film on aluminum . . . 206 (2003) 691
Li, Q., see Feng, T. . . . 206 (2003) 198
Li, W.J., Z.R. Song, Y.H. Yu, S.C. Zou and D. Shen, Determination of sp^3/sp^2 ratio in amorphous-carbon thin film synthesized by reactive filtered arc deposition . . . 206 (2003) 339
Li, Z.F., see Hu, L. . . . 206 (2003) 127
Liang, J.H. and S.L. Chiang, Characterization of BSi molecular ion implantation . . . 206 (2003) 932
Librant, Z., see Jagielski, J. . . . 206 (2003) 1097
Lien, S.C., see Doyle, J.P. . . . 206 (2003) 467
Lim, J.-W., K. Mimura, K. Miyake, M. Yamashita and M. Isshiki, Preparation of high-purity Cu films by non-mass separated ion beam deposition . . . 206 (2003) 371
Lim, S.H.N., see McKenzie, D.R. . . . 206 (2003) 741
Lindner, J.K.N., see Häberlen, M. . . . 206 (2003) 916
Lindner, J.K.N., see Kögler, R. . . . 206 (2003) 989
Liu, B.X., see Hu, L. . . . 206 (2003) 127
Liu, C., see Matsutani, T. . . . 206 (2003) 343
Liu, C., T. Matsutani, T. Asanuma and M. Kiuchi, Structural, electrical and optical properties of indium tin oxide films prepared by low-energy oxygen-ion-beam assisted deposition . . . 206 (2003) 348
Liu, J., see Shao, L. . . . 206 (2003) 413
Liu, X., see Feng, T. . . . 206 (2003) 198
Lopatin, O.N., see Khaibullin, R.I. . . . 206 (2003) 277
Lourenço, M.A., R.M. Gwilliam, G. Shao and K.P. Homewood, Dislocation engineered β-$FeSi_2$ light emitting diodes . . . 206 (2003) 436
Lu, H.F., C. Zhang and Q.Y. Zhang, Adatom, vacancy and sputtering yields of low energy Pt atoms impacts on Pt(1 1 1) by molecular dynamics simulation . . . 206 (2003) 22
Lu, M., see Doyle, J.P. . . . 206 (2003) 467
Luther-Davies, B., see Elliman, R.G. . . . 206 (2003) 427

Ma, X.X., K. Yukimura and T. Muraho, Ion sheath evolution and plasma replenishment inside an 80-mm-diameter pipe for plasma-based ion implantation and deposition . . . 206 (2003) 787
Ma, X.X., K. Yukimura, T. Ikehata and Y. Miyagawa, Ion current on the inner surface of a pipe by plasma-based ion implantation and deposition . . . 206 (2003) 813
Maeda, K., see Koguchi, Y. . . . 206 (2003) 202
Maekawa, M., see Yamaki, T. . . . 206 (2003) 254
Maekawa, M., Y. Hase, N. Shikazono and A. Tanaka, Induction of somatic instability in stable yellow leaf mutant of rice by ion beam irradiation . . . 206 (2003) 579
Mändl, S., R. Sader, G. Thorwarth, D. Krause, H.-F. Zeilhofer, H.H. Horch and B. Rauschenbach, Biocompatibility of titanium based implants treated with plasma immersion ion implantation . . . 206 (2003) 517
Mändl, S., D. Manova and B. Rauschenbach, Interplay of surface adsorption and preferential sputtering in metal plasma immersion ion implantation and deposition . . . 206 (2003) 663

Mändl, S., J.W. Gerlach, W. Assmann and B. Rauschenbach, Thickness of ion implanted layers as determined by elastic recoil detection analysis and spectroscopic ellipsometry . . . 206 (2003) 668
Mändl, S., see Rauschenbach, B. . . . 206 (2003) 803
Manova, D., see Mändl, S. . . . 206 (2003) 663
Marchal, J., A. Al-Ajili, J. Scott, D. Doak, M. Abdalla, R. Gwilliam, Ch. Fröjdh, V. O'Shea, K. Smith and M. Rahman, A new pixel sensor for uniformity control in ion implantation . . . 206 (2003) 462
Marks, N.A., see McKenzie, D.R. . . . 206 (2003) 741
Markwitz, A., V.J. Kennedy and H. Baumann, Formation of micrometer sized crater shaped pits in silicon by low-energy $^{22}Ne^{+}$ implantation and electron beam annealing . . . 206 (2003) 179
Markwitz, A., see Johnson, P.B. . . . 206 (2003) 1056
Maruyama, T., see Yukimura, K. . . . 206 (2003) 745
Masamune, S. and K. Yukimura, Ion implantation to inner surface of a cylinder . . . 206 (2003) 682
Mase, H., see Ikehata, T. . . . 206 (2003) 772
Mase, H., see Ikehata, T. . . . 206 (2003) 782
Matsubayashi, N., see Saito, T. . . . 206 (2003) 321
Matsuda, S., see Sumita, T. . . . 206 (2003) 448
Matsui, S., see Fujita, J. . . . 206 (2003) 472
Matsui, S., see Kanda, K. . . . 206 (2003) 880
Matsui, S., see Kitagawa, T. . . . 206 (2003) 884
Matsui, S., see Miyauchi, K. . . . 206 (2003) 893
Matsumura, S., see Bae, In.-T. . . . 206 (2003) 974
Matsumura, Y., see Takeuchi, M. . . . 206 (2003) 259
Matsunami, N., M. Itoh, Y. Takai, M. Tazawa and M. Sataka, Ion beam modification of ZnO thin films on MgO 206 (2003) 282
Matsuo, J., see Yamada, I. . . . 206 (2003) 820
Matsuo, J., T. Seki, T. Aoki and I. Yamada, Atomistic study of cluster collision on solid surfaces . . . 206 (2003) 838
Matsuo, J., see Nakai, A. . . . 206 (2003) 842
Matsuo, J., see Birtcher, R.C. . . . 206 (2003) 851
Matsuo, J., see Aoki, T. . . . 206 (2003) 855
Matsuo, J., see Aoki, T. . . . 206 (2003) 861
Matsuo, J., see Nakatsu, O. . . . 206 (2003) 866
Matsuo, J., see Kitagawa, T. . . . 206 (2003) 884
Matsuo, J., see Seki, T. . . . 206 (2003) 902
Matsutani, T., see Ensinger, W. . . . 206 (2003) 334
Matsutani, T., T. Asanuma, C. Liu, M. Kiuchi and T. Takeuchi, Comparison of surface morphologies of SiO_2 films prepared by ion-beam induced chemical vapor deposition and ion-beam assisted deposition . . . 206 (2003) 343
Matsutani, T., see Liu, C. . . . 206 (2003) 348
Matz, W., see Piatkowska, A. . . . 206 (2003) 1052
McCormick, A.W., see Rehn, L.E. . . . 206 (2003) 490
McCormick, A.W., see Birtcher, R.C. . . . 206 (2003) 851
McCulloch, D.G., see McKenzie, D.R. . . . 206 (2003) 741
McKenzie, D.R., R.N. Tarrant, M.M.M. Bilek, G. Pearce, N.A. Marks, D.G. McCulloch and S.H.N. Lim, Voltage dependence of cluster size in carbon films using plasma immersion ion implantation . . . 206 (2003) 741
Meguro, T., see Koguchi, Y. . . . 206 (2003) 202
Mikhailova, G.N., see Bayazitov, R.M. . . . 206 (2003) 984
Milanez Silva, C., P. Varisco, A. Moehlecke, P.P. Fichtner, R.M. Papaléo and J. Eriksson, Processing of nano-holes and pores on SiO_2 thin films by MeV heavy ions . . . 206 (2003) 486
Mimura, K., see Lim, J.-W. . . . 206 (2003) 371
Mirabella, S., see De Salvador, D. . . . 206 (2003) 922
Miranda, R.M.N., see Heck, C. . . . 206 (2003) 601
Misaka, J., see Yamashita, H. . . . 206 (2003) 889
Mitamura, T., see Fujiwara, Y. . . . 206 (2003) 870
Mitamura, T., see Miyauchi, K. . . . 206 (2003) 893
Mitsuhashi, T., see Sakaguchi, I. . . . 206 (2003) 153
Mitsuishi, K., M. Song, K. Furuya, C.W. Allen, R.C. Birtcher and U. Dahmen, Effect of aspect ratio on phase changes of rare-gas precipitates in an Al matrix . . . 206 (2003) 109
Mitsuo, A., T. Mori, Y. Setsuhara, S. Miyake and T. Aizawa, Mechanical properties of zirconium films prepared by ion-beam assisted deposition . . . 206 (2003) 366

Miyagawa, S., see Miyagawa, Y. . . . 206 (2003) 767
Miyagawa, Y., see Djurabekova, F.G. . . . 206 (2003) 194
Miyagawa, Y., M. Ikeyama, S. Miyagawa and H. Nakadate, Computer simulation of plasma for plasma immersed ion implantation and deposition with bipolar pulses . . . 206 (2003) 767
Miyagawa, Y., see Ma, X.X. . . . 206 (2003) 813
Miyake, K., see Lim, J.-W. . . . 206 (2003) 371
Miyake, S., see Mitsuo, A. . . . 206 (2003) 366
Miyao, M., see Murakami, Y. . . . 206 (2003) 304
Miyao, M., see Sadoh, T. . . . 206 (2003) 478
Miyashita, A., see Sumita, T. . . . 206 (2003) 245
Miyauchi, K., see Kitagawa, T. . . . 206 (2003) 884
Miyauchi, K., T. Kitagawa, N. Toyoda, S. Matsui, K. Mochiji, T. Mitamura and I. Yamada, Optimization of flux ratio of C_{60} molecule to Ar cluster ion for diamond-like carbon film deposition by NEXAFS measurement . . . 206 (2003) 893
Mizuno, G., see Tanaka, T. . . . 206 (2003) 817
Mizutani, D., see Sakudo, N. . . . 206 (2003) 687
Mochiji, K., see Fujiwara, Y. . . . 206 (2003) 870
Mochiji, K., see Miyauchi, K. . . . 206 (2003) 893
Moehlecke, A., see Milanez Silva, C. . . . 206 (2003) 486
Mokuno, Y., see Fukumi, K. . . . 206 (2003) 353
Mokuno, Y., see Tojo, H. . . . 206 (2003) 717
Monteiro, T., see Alves, E. . . . 206 (2003) 148
Monteiro, T., see Alves, E. . . . 206 (2003) 1047
Moon, J.H., see Hishita, S. . . . 206 (2003) 171
Mori, H., T. Hirao, J.S. Laird, S. Onoda, T. Wakasa, T. Yamakawa, H. Itoh, T. Okamoto and Y. Koizumi, Modeling of transient charge collection induced by an angled single ion strike . . . 206 (2003) 31
Mori, H., see Laird, J.S. . . . 206 (2003) 36
Mori, H., see Arakawa, K. . . . 206 (2003) 76
Mori, H., see Onoda, S. . . . 206 (2003) 444
Mori, H., see Hirao, T. . . . 206 (2003) 457
Mori, T., see Mitsuo, A. . . . 206 (2003) 366
Morishita, N., see Isoya, J. . . . 206 (2003) 965
Morishita, T., see Yamaguchi, H. . . . 206 (2003) 561
Morishita, T., H. Yamaguchi, K. Degi, N. Shikazono, Y. Hase, A. Tanaka and T. Abe, Dose response and mutation induction by ion beam irradiation in buckwheat . . . 206 (2003) 565
Morita, K., H. Suzuki and K. Soda, Creation of hydrogen gas emitting function in proton conducting oxide ceramics by hydrogen implantation . . . 206 (2003) 228
Moriwaki, T., see Hayashi, N. . . . 206 (2003) 1066
Motohashi, Y., see Shibata, T. . . . 206 (2003) 139
Motohashi, Y., T. Kobayashi, S. Harjo, T. Sakuma, T. Shibata, M. Ishihara, S. Baba and T. Hoshiya, Radiation damage effects in superplastic 3Y-TZP irradiated with Zr ions . . . 206 (2003) 144
Motono, M., see Tsuji, H. . . . 206 (2003) 615
Motono, M., see Arai, N. . . . 206 (2003) 629
Mozetic, M., see Piatkowska, A. . . . 206 (2003) 1052
Mücklich, A., see Kögler, R. . . . 206 (2003) 989
Mukaigawa, S., S. Kanno, K. Takaki and T. Fujiwara, Measurements of heat flux distribution toward substrate by means of the $LiNbO_3$ interferometer, and electron density in a capacitively coupled rf discharge plasma . . . 206 (2003) 777
Mukaigawa, S., see Takaki, K. . . . 206 (2003) 794
Mukumoto, Y., see Ono, F. . . . 206 (2003) 295
Müller, C., see Ono, F. . . . 206 (2003) 295
Muraho, T., see Yukimura, K. . . . 206 (2003) 745
Muraho, T., see Ma, X.X. . . . 206 (2003) 787
Muraho, T., see Yukimura, K. . . . 206 (2003) 791
Murakami, Y., I. Tsunoda, H. Kido, A. Kenjo, T. Sadoh, M. Miyao and T. Yoshitake, Enhanced solid-phase growth of β-$FeSi_2$ by pre-amorphization . . . 206 (2003) 304
Muramatsu, H., see Watanabe, S. . . . 206 (2003) 399

Nagaoka, S., see Okuyama, Y. 206 (2003) 543
Nagata, S., see Takahiro, K. 206 (2003) 206
Nagata, S., see Wei, P. 206 (2003) 233
Nagata, S., see Takahiro, K. 206 (2003) 639
Nagatomi, S., see Yamaguchi, H. 206 (2003) 561
Naito, M., see Ishimaru, M. 206 (2003) 994
Nakadate, H., see Miyagawa, Y. 206 (2003) 767
Nakagawa, S.T., Crystallographic analysis of the amorphization caused by ion irradiation: Self-irradiation . . 206 (2003) 13
Nakagawa, Y., see Doyle, J.P. 206 (2003) 467
Nakai, A., T. Aoki, T. Seki, J. Matsuo, G.H. Takaoka and I. Yamada, Modeling of surface smoothing process by cluster ion beam irradiation 206 (2003) 842
Nakajima, H., see Kurotobi, K. 206 (2003) 532
Nakamura, K., see Yokota, K. 206 (2003) 386
Nakamura, K., M. Ando and H. Sugai, Photon-enhanced secondary electron emission at target in plasma immersion ion implantation 206 (2003) 798
Nakamura, T., H. Tanabe, T. Hitomi and M. Satoh, Electrical properties of the regrown implantation-induced amorphous layer on (1 $\bar{1}$ 0 0)- and (1 1 $\bar{2}$ 0)-oriented 6H-SiC 206 (2003) 956
Nakanishi, Y., A. Wakahara, H. Okada, A. Yoshida, T. Ohshima, H. Itoh, S. Nakao, K. Saito and Y.T. Kim, Effects of implantation conditions on the luminescence properties of Eu-doped GaN 206 (2003) 1033
Nakano, H., see Doyle, J.P. 206 (2003) 467
Nakano, S., see Wang, Q. 206 (2003) 118
Nakano, S., see Ogiso, H. 206 (2003) 157
Nakanoya, T., see Haraguchi, M. 206 (2003) 313
Nakanoya, T., see Saito, T. 206 (2003) 321
Nakao, A., M. Iwaki and Y. Yokoyama, Potassium ion implantation into glassy carbon 206 (2003) 211
Nakao, A., see Kobayashi, T. 206 (2003) 1110
Nakao, H., see Yamashita, H. 206 (2003) 889
Nakao, H., see Yamashita, H. 206 (2003) 898
Nakao, S., see Nakanishi, Y. 206 (2003) 1033
Nakashima, K., see Abe, K. 206 (2003) 960
Nakashima, K., see Eryu, O. 206 (2003) 969
Nakatani, Y., see Yamashita, H. 206 (2003) 898
Nakatsu, O., J. Matsuo, K. Omoto, T. Seki, G. Takaoka and I. Yamada, Titanium-dioxide film formation using gas cluster ion beam assisted deposition technique 206 (2003) 866
Nakazawa, T., V. Grismanovs, D. Yamaki, Y. Katano and T. Aruga, Disordering in Li_2TiO_3 irradiated with high energy ions 206 (2003) 166
Namba, H., see Koizumi, H. 206 (2003) 1124
Napolitani, E., see De Salvador, D. 206 (2003) 922
Naramoto, H., see Ookawa, R. 206 (2003) 175
Naramoto, H., see Takahiro, K. 206 (2003) 206
Naramoto, H., see Wei, P. 206 (2003) 233
Naramoto, H., see Yamamoto, S. 206 (2003) 268
Naramoto, H., see Vacik, J. 206 (2003) 395
Naramoto, H., see Takahiro, K. 206 (2003) 639
Naramoto, H., see Kitazawa, S.-i. 206 (2003) 952
Narumi, K., see Hirata, K. 206 (2003) 47
Narumi, K., see Takahiro, K. 206 (2003) 206
Narumi, K., see Wei, P. 206 (2003) 233
Narumi, K., see Vacik, J. 206 (2003) 395
Narumi, K., see Kitazawa, S.-i. 206 (2003) 952
Nastasi, M., see Afanasyev-Charkin, I.V. 206 (2003) 736
Nastasi, M., see Verda, R.D. 206 (2003) 927
Nastasi, M., see Swadener, J.G. 206 (2003) 937
Natsuhori, M., see Wada, S. 206 (2003) 553
Neumann, H., see Chassé, T. 206 (2003) 377
Neumann, R., see Ono, F. 206 (2003) 295
Nishigaito, S., see Wada, M. 206 (2003) 557

Nishii, J., see Fukumi, K. . . . 206 (2003) 353
Nishimura, Y., R. Ohkawa, H. Oka, H. Akamatsu, K. Azuma and M. Yatsuzuka, Uniform coating of thick DLC film on three-dimensional substrates . . . 206 (2003) 696
Nishimura, Y., see Oka, Y. . . . 206 (2003) 700
Nishiyama, F., see Ookawa, R. . . . 206 (2003) 175
Nishiyama, F., see Takahiro, K. . . . 206 (2003) 206
Nitta, N and M. Taniwaki, Novel nano-fabrication technique utilizing ion beam . . . 206 (2003) 482
Nordlund, K., see Pomoell, J. . . . 206 (2003) 18
Nordlund, K., see Peltola, J. . . . 206 (2003) 61
Nordlund, K., see Frantz, J. . . . 206 (2003) 66
Nordlund, K., J. Tarus, J. Keinonen, S.E. Donnelly and R.C. Birtcher, Atomic fingers, bridges and slingshots: formation of exotic surface structures during ion irradiation of heavy metals . . . 206 (2003) 189
Nurutdinov, R.M., see Bayazitov, R.M. . . . 206 (2003) 984

Ochiai, Y., see Fujita, J. . . . 206 (2003) 472
Odahara, S., see Doyle, J.P. . . . 206 (2003) 467
Ogiso, H., see Wang, Q. . . . 206 (2003) 118
Ogiso, H., S. Nakano and J. Akedo, Abnormal distribution of defects introduced into MgO single crystals by MeV ion implantation . . . 206 (2003) 157
Ohashi, N., see Sakaguchi, I. . . . 206 (2003) 153
Ohashi, O., see Wang, A. . . . 206 (2003) 219
Ohi, A., see Sumita, T. . . . 206 (2003) 448
Ohi, A., see Isoya, J. . . . 206 (2003) 965
Ohkawa, R., see Nishimura, Y. . . . 206 (2003) 696
Ohmido, N., see Kitamura, S. . . . 206 (2003) 548
Ohmura, Y., see Sakudo, N. . . . 206 (2003) 687
Ohnishi, M., see Yokota, K. . . . 206 (2003) 386
Ohshima, T., see Sumita, T. . . . 206 (2003) 448
Ohshima, T., see Isoya, J. . . . 206 (2003) 965
Ohshima, T., K.K. Lee, S. Onoda, T. Kamiya, M. Oikawa, J.S. Laird, T. Hirao and H. Itoh, Observation of transient current induced in silicon carbide diodes by ion irradiation . . . 206 (2003) 979
Ohshima, T., see Nakanishi, Y. . . . 206 (2003) 1033
Ohtsuka, M., see Okamura, M. . . . 206 (2003) 574
Ohya, K., Comparative study of target atomic number dependence of ion induced and electron induced secondary electron emission . . . 206 (2003) 52
Oikawa, M., see Ohshima, T. . . . 206 (2003) 979
Oka, H., see Nishimura, Y. . . . 206 (2003) 696
Oka, Y., M. Tao, Y. Nishimura, K. Azuma, E. Fujiwara and M. Yatsuzuka, Properties of thick DLC films prepared by plasma-based ion implantation and deposition using combined RF and H.V. pulses . . . 206 (2003) 700
Okada, H., see Nakanishi, Y. . . . 206 (2003) 1033
Okamoto, T., see Mori, H. . . . 206 (2003) 31
Okamoto, T., see Onoda, S. . . . 206 (2003) 444
Okamura, M., N. Yasuno, M. Ohtsuka, A. Tanaka, N. Shikazono and Y. Hase, Wide variety of flower-color and -shape mutants regenerated from leaf cultures irradiated with ion beams . . . 206 (2003) 574
Okazaki, N., see Doyle, J.P. . . . 206 (2003) 467
Okubo, N., N. Umeda, Y. Takeda and N. Kishimoto, Enhancement of metal-nanoparticle precipitation by co-irradiation of high-energy heavy ions and laser in silica glass . . . 206 (2003) 610
Okubo, N., see Kishimoto, N. . . . 206 (2003) 634
Okubo, N., see Amekura, H. . . . 206 (2003) 1101
Okuyama, Y., M. Sato, S. Nagaoka, H. Kawakami, Y. Suzuki and M. Iwaki, Neurite outgrowth on fluorinated polyimide film micropatterned by ion irradiation . . . 206 (2003) 543
Omoto, K., see Nakatsu, O. . . . 206 (2003) 866
Ono, F., Y. Hamatani, Y. Mukumoto, S. Komatsu, N. Ishikawa, Y. Chimi, A. Iwase, T. Kambara, C. Müller and R. Neumann, Modification of Fe–Ni Invar alloys by high-energy ion beams . . . 206 (2003) 295
Ono, K., see Arakawa, K. . . . 206 (2003) 76
Ono, K., K. Arakawa and R.C. Birtcher, Intermittent rapid motion of helium bubbles in Cu during irradiation with high energy self-ions . . . 206 (2003) 114

Onoda, S., see Mori, H. . . . 206 (2003) 31
Onoda, S., see Laird, J.S. . . . 206 (2003) 36
Onoda, S., T. Hirao, J.S. Laird, H. Mori, H. Itoh, T. Wakasa, T. Okamoto and Y. Koizumi, Displacement damage degradation of ion-induced charge in Si pin photodiode . . . 206 (2003) 444
Onoda, S., see Hirao, T. . . . 206 (2003) 457
Onoda, S., see Ohshima, T. . . . 206 (2003) 979
Onozaki, Y., see Takeuchi, M. . . . 206 (2003) 259
Oohashi, G., see Suzuki, Y. . . . 206 (2003) 538
Ookawa, R., K. Takahiro, K. Kawatsura, F. Nishiyama, S. Yamamoto and H. Naramoto, Structure of amorphized C_{60} films studied by Raman spectroscopy and X-ray photoelectron spectroscopy . . . 206 (2003) 175
Ookawa, R., see Takahiro, K. . . . 206 (2003) 206
Osaka, M., see Kasukabe, Y. . . . 206 (2003) 390
Oseki, T., see Hayashi, K. . . . 206 (2003) 403
O'Shea, V., see Marchal, J. . . . 206 (2003) 462
Otani, T., see Kitahara, N. . . . 206 (2003) 999
Otto, G., see Hobler, G. . . . 206 (2003) 81

Panca Putra, T.Y.S., see Kitazawa, S.-i. . . . 206 (2003) 952
Papaléo, R.M., R. Leal, C. Trautmann and E.M. Bringa, Cratering by MeV–GeV ions as a function of angle of incidence . . . 206 (2003) 7
Papaléo, R.M., see Milanez Silva, C. . . . 206 (2003) 486
Parhomenko, Yu.N., see Gerasimenko, N.N. . . . 206 (2003) 644
Park, C.H., J.Y. Lee, S. Im and T.G. Kim, n-ZnO/p-Si photodiodes fabricated using ion-beam induced isolation technique . . . 206 (2003) 432
Park, D., see Sakaguchi, I. . . . 206 (2003) 153
Pavluchenko, M.N., see Gerasimenko, N.N. . . . 206 (2003) 299
Pavluchenko, M.N., see Gerasimenko, N.N. . . . 206 (2003) 644
Pearce, G., see McKenzie, D.R. . . . 206 (2003) 741
Peeva, A., R. Koegler and W. Skorupa, Visualization of vacancy type defects in the $R_P/2$ region of ion implanted and annealed silicon . . . 206 (2003) 71
Peeva, A., see Angelov, Ch. . . . 206 (2003) 907
Peltola, J., K. Nordlund and J. Keinonen, Heat spike effect on the straggling of cluster implants . . . 206 (2003) 61
Peng, P., see Tian, X.B. . . . 206 (2003) 673
Peng, P., see Tang, D.L. . . . 206 (2003) 808
Pereira, S., see Alves, E. . . . 206 (2003) 1042
Péter, Á., see Kling, A. . . . 206 (2003) 653
Phanchaisri, B., see Yu, L.D. . . . 206 (2003) 586
Piatkowska, A., J. Jagielski, M. Kopcewicz, W. Matz, A. Zalar and M. Mozetic, Structural properties of ion beam mixed tungsten/steel layers . . . 206 (2003) 1052
Piatkowska, A., see Jagielski, J. . . . 206 (2003) 1097
Piazza, F., see Golanski, A. . . . 206 (2003) 731
Pinto, J.V., see Alves, E. . . . 206 (2003) 148
Pipeleers, B., S.M. Hogg and A. Vantomme, Influence of the implantation angle on the generation of defects for Er implanted GaN . . . 206 (2003) 95
Plaksin, O.A., V.A. Stepanov, P.V. Demenkov, P.A. Stepanov, V.A. Skuratov and N. Kishimoto, Radioluminescence of alumina during proton and heavy ion irradiation . . . 206 (2003) 1083
Poirier, R., V. Avalos, S. Dannefaer, F. Schiettekatte and S. Roorda, Divacancies in proton irradiated silicon: Comparison of annealing mechanisms studied with infrared spectroscopy and positron annihilation . . . 206 (2003) 85
Pomoell, J., A.V. Krasheninnikov, K. Nordlund and J. Keinonen, Stopping of energetic ions in carbon nanotubes . . . 206 (2003) 18
Popok, V.N., see Khaibullin, R.I. . . . 206 (2003) 1115
Priolo, F., see De Salvador, D. . . . 206 (2003) 922
Purwanto, S., I. Sakamoto, M. Koike, H. Tanoue and S. Honda, Effects of ion irradiation on structural and magnetic properties of Fe/Si multilayers prepared by helicon plasma sputtering . . . 206 (2003) 326

Rahman, M., see Marchal, J. . . . 206 (2003) 462
Raineri, V., see De Salvador, D. . . . 206 (2003) 922

Rameev, B.Z., see Khaibullin, R.I. 206 (2003) 1115
Rangan, S., S. Ashok, G. Chen and D. Theodore, Multi-layered nanocavities in silicon with sequential helium implantation/anneal 206 (2003) 417
Rauschenbach, B., see Chassé, T. 206 (2003) 377
Rauschenbach, B., see Mändl, S. 206 (2003) 517
Rauschenbach, B., see Mändl, S. 206 (2003) 663
Rauschenbach, B., see Mändl, S. 206 (2003) 668
Rauschenbach, B. and S. Mändl, Plasma-sheath expansion around trenches in plasma immersion ion implantation 206 (2003) 803
Rauschenbach, B., see Hammerl, C. 206 (2003) 1072
Rehn, L.E., B.J. Kestel, P.M. Baldo, J. Hiller, A.W. McCormick and R.C. Birtcher, Self-organized porous-alumina implantation masks for generating nanoscale arrays 206 (2003) 490
Reuther, H., see Ueda, M. 206 (2003) 749
Reuther, H., see Kögler, R. 206 (2003) 989
Ridgway, M.C., see Ruault, M.-O. 206 (2003) 912
Ridgway, M.C., see de M. Azevedo, G. 206 (2003) 1024
Rita, E., see Alves, E. 206 (2003) 1047
Roorda, S., see Poirier, R. 206 (2003) 85
Rossi, J.O., see Ueda, M. 206 (2003) 760
Roudil, D., see Trocellier, P. 206 (2003) 1077
Ruault, M.-O., M.C. Ridgway, F. Fortuna, H. Bernas and J.S. Williams, Shrinkage mechanism of nanocavities in amorphous Si under ion irradiation: An in situ study 206 (2003) 912
Ryasnyansky, A.I., see Stepanov, A.L. 206 (2003) 624

Sader, R., see Mändl, S. 206 (2003) 517
Sadoh, T., see Murakami, Y. 206 (2003) 304
Sadoh, T., H. Eguchi, A. Kenjo and M. Miyao, Etching characteristics of SiO_2 irradiated with focused ion beam 206 (2003) 478
Saito, H., see Yukimura, K. 206 (2003) 745
Saito, K., see Nakanishi, Y. 206 (2003) 1033
Saito, R., see Fukudome, T. 206 (2003) 287
Saito, T., see Yamamoto, H. 206 (2003) 42
Saito, T., see Haraguchi, M. 206 (2003) 313
Saito, T., H. Yamamoto, K. Yamaguchi, T. Nakanoya, K. Hojou, M. Haraguchi, M. Imamura, N. Matsubayashi, T. Tanaka and H. Shimada, Characterization of air-exposed surface of β-$FeSi_2$ fabricated by ion beam sputter deposition method 206 (2003) 321
Saito, Y., Y. Imamura and A. Kitahara, Optical properties of YSZ implanted with Ag ions 206 (2003) 272
Saitoh, H., see Choi, Y. 206 (2003) 241
Saitoh, K., see Arakawa, K. 206 (2003) 76
Saitoh, Y., see Hirata, K. 206 (2003) 47
Saitoh, Y., see Doyle, J.P. 206 (2003) 467
Sakaguchi, I., D. Park, Y. Takata, S. Hishita, N. Ohashi, H. Haneda and T. Mitsuhashi, An effect of annealing on In implanted ZnO 206 (2003) 153
Sakai, K., see Doyle, J.P. 206 (2003) 467
Sakai, S., see Kitazawa, S.-i. 206 (2003) 952
Sakamoto, I., see Purwanto, S. 206 (2003) 326
Sakamoto, I., see Hayashi, N. 206 (2003) 1066
Sakudo, N., D. Mizutani, Y. Ohmura, H. Endo, R. Yoneda, N. Ikenaga and H. Takikawa, Surface modification of PET film by plasma-based ion implantation 206 (2003) 687
Sakuma, T., see Shibata, T. 206 (2003) 139
Sakuma, T., see Motohashi, Y. 206 (2003) 144
Sang, J., see Zhang, X. 206 (2003) 215
Santeufemio, C., see Insepov, Z. 206 (2003) 846
Sasase, M., see Haraguchi, M. 206 (2003) 313
Sasase, M., see Takahiro, K. 206 (2003) 639
Sataka, M., see Matsunami, N. 206 (2003) 282
Sato, H., see Tsuji, H. 206 (2003) 507
Sato, M., see Okuyama, Y. 206 (2003) 543

Sato, N.Y., see Ikehata, T. . . . 206 (2003) 772
Sato, N.Y., see Ikehata, T. . . . 206 (2003) 782
Satoh, H., see Doyle, J.P. . . . 206 (2003) 467
Satoh, M., see Nakamura, T. . . . 206 (2003) 956
Saudé, S., see Trocellier, P. . . . 206 (2003) 1077
Savoini, B., see Alves, E. . . . 206 (2003) 148
Sawa, M., see Enomoto, Y. . . . 206 (2003) 596
Schiettekatte, F., see Poirier, R. . . . 206 (2003) 85
Schloesser, K., see Golombeck, M.-A. . . . 206 (2003) 495
Schuessler, B., see Golombeck, M.-A. . . . 206 (2003) 495
Schulze, S., see Golanski, A. . . . 206 (2003) 731
Schweickert, H., see Golombeck, M.-A. . . . 206 (2003) 495
Scott, J., see Marchal, J. . . . 206 (2003) 462
Sealy, B.J., see Ahmed, S. . . . 206 (2003) 1003
Sealy, B.J., see Ahmed, S. . . . 206 (2003) 1008
Seki, T., see Matsuo, J. . . . 206 (2003) 838
Seki, T., see Nakai, A. . . . 206 (2003) 842
Seki, T., see Nakatsu, O. . . . 206 (2003) 866
Seki, T., J. Matsuo, G.H. Takaoka and I. Yamada, Generation of the large current cluster ion beam . . . 206 (2003) 902
Sekine, T., see Watanabe, S. . . . 206 (2003) 399
Senna, J.R., see Beloto, A.F. . . . 206 (2003) 677
Sermanni, P., see Donnelly, S.E. . . . 206 (2003) 422
Serruys, Y., see Trocellier, P. . . . 206 (2003) 1077
Setsuhara, Y., see Mitsuo, A. . . . 206 (2003) 366
Shao, G., see Gao, Y. . . . 206 (2003) 317
Shao, G., see Lourenço, M.A. . . . 206 (2003) 436
Shao, L., J. Liu, X. Wang, H. Chen, P.E. Thompson and W.-K. Chu, Reduction of boride-enhanced diffusion by point defect engineering and its application for shallow junction formation . . . 206 (2003) 413
Sharma, A., see Singh, N. . . . 206 (2003) 1120
Shen, D., see Li, W.J. . . . 206 (2003) 339
Shibata, H., see Koshimizu, M. . . . 206 (2003) 57
Shibata, T., M. Ishihara, Y. Motohashi, S. Baba, T. Hoshiya, T. Kobayashi, S. Harjo and T. Sakuma, Superplastic deformation characteristics of 3Y-TZP after Zr ion irradiation . . . 206 (2003) 139
Shibata, T., see Motohashi, Y. . . . 206 (2003) 144
Shibuya, K., see Koshimizu, M. . . . 206 (2003) 57
Shiiyama, K., see Higuchi, T. . . . 206 (2003) 103
Shikazono, N., see Yamaguchi, H. . . . 206 (2003) 561
Shikazono, N., see Morishita, T. . . . 206 (2003) 565
Shikazono, N., see Ishii, K. . . . 206 (2003) 570
Shikazono, N., see Okamura, M. . . . 206 (2003) 574
Shikazono, N., see Maekawa, M. . . . 206 (2003) 579
Shimada, H., see Saito, T. . . . 206 (2003) 321
Shimatsu, K., see Ikehata, T. . . . 206 (2003) 782
Shimizugawa, Y., see Kanda, K. . . . 206 (2003) 880
Shimomura, H., see Watanabe, S. . . . 206 (2003) 399
Shinohara, M., see Yoshida, M. . . . 206 (2003) 712
Shiota, Y., see Doyle, J.P. . . . 206 (2003) 467
Shioya, K., see Ikehata, T. . . . 206 (2003) 772
Short, K.T., see Johnson, P.B. . . . 206 (2003) 1056
Shutthanandan, V., see Thevuthasan, S. . . . 206 (2003) 162
Sickafus, K.E., see Bae, In.-T. . . . 206 (2003) 974
Sickafus, K.E., see Ishimaru, M. . . . 206 (2003) 994
Sielemann, R., see Weyer, G. . . . 206 (2003) 90
Silva, M.D., see Beloto, A.F. . . . 206 (2003) 677
Simeone, D., see Trocellier, P. . . . 206 (2003) 1077
Singh, N., A. Sharma and D.K. Avasthi, Effects of high energy (MeV) ion beam irradiation on polyethylene terephthalate . . . 206 (2003) 1120

Sittner, F., see Ensinger, W. 206 (2003) 334
Skobochkin, A.M., see Gerasimenko, N.N. 206 (2003) 299
Skorupa, W., see Peeva, A. 206 (2003) 71
Skorupa, W., see Angelov, Ch. 206 (2003) 907
Skorupa, W., see Kögler, R. 206 (2003) 989
Skuratov, V.A., see Plaksin, O.A. 206 (2003) 1083
Smith, K., see Marchal, J. 206 (2003) 462
Smith, N., see Elliman, R.G. 206 (2003) 427
Soares, J., see Alves, E. 206 (2003) 1047
Soares, J.C., see Kling, A. 206 (2003) 653
Soda, K., see Morita, K. 206 (2003) 228
Song, J.H., see Jeon, G.Y. 206 (2003) 409
Song, J.-H., see Jeon, G.Y. 206 (2003) 409
Song, M., see Mitsuishi, K. 206 (2003) 109
Song, Z.R., see Li, W.J. 206 (2003) 339
Stepanov, A.L., R.A. Ganeev, A.I. Ryasnyansky and T. Usmanov, Non-linear optical properties of metal nanoparticles implanted in silicate glass 206 (2003) 624
Stepanov, P.A., see Plaksin, O.A. 206 (2003) 1083
Stepanov, V.A., see Plaksin, O.A. 206 (2003) 1083
Stoquert, J.P., see Golanski, A. 206 (2003) 731
Stritzker, B., see Häberlen, M. 206 (2003) 916
Suga, T., see Bandourko, V. 206 (2003) 606
Suga, T., Y. Takeda, K. Kono, N. Kishimoto, V.V. Bandourko and C.G. Lee, Radiation effects in diamond induced by negative gold ions 206 (2003) 947
Sugahara, H., see Tsuji, H. 206 (2003) 249
Sugai, H., see Nakamura, K. 206 (2003) 798
Sumita, T., see Choi, Y. 206 (2003) 241
Sumita, T., T. Yamaki, S. Yamamoto and A. Miyashita, Ion beam modification of photo-induced charge separation in TiO_2 films 206 (2003) 245
Sumita, T., see Yamaki, T. 206 (2003) 254
Sumita, T., see Umebayashi, T. 206 (2003) 264
Sumita, T., M. Imaizumi, S. Matsuda, T. Ohshima, A. Ohi and H. Itoh, Proton radiation analysis of multi-junction space solar cells 206 (2003) 448
Suzuki, H., see Morita, K. 206 (2003) 228
Suzuki, H., see Kurotobi, K. 206 (2003) 532
Suzuki, Y., see Xu, G.C. 206 (2003) 330
Suzuki, Y., Ion beam modification of polymers for the application of medical devices 206 (2003) 501
Suzuki, Y., see Yotoriyama, T. 206 (2003) 527
Suzuki, Y., see Kurotobi, K. 206 (2003) 532
Suzuki, Y., M. Iwaki, S. Tani, G. Oohashi and M. Kamio, Ion implantation into ePTFE for application of a dural substitute 206 (2003) 538
Suzuki, Y., see Okuyama, Y. 206 (2003) 543
Swadener, J.G. and M. Nastasi, Increasing the fracture toughness of silicon by ion implantation 206 (2003) 937

Tabacniks, M.H., see Ueda, M. 206 (2003) 760
Taguchi, M., see Koizumi, H. 206 (2003) 1124
Takagi, T., see Yoshida, M. 206 (2003) 712
Takagi, T., see Tanaka, T. 206 (2003) 817
Takahiro, K., see Ookawa, R. 206 (2003) 175
Takahiro, K., R. Ookawa, K. Kawatsura, F. Nishiyama, S. Nagata, S. Yamamoto, K. Narumi, H. Naramoto and M. Iwaki, Surface morphology of glassy carbon irradiated with nitrogen ions 206 (2003) 206
Takahiro, K., K. Kawatsura, S. Nagata, S. Yamamoto, H. Naramoto, M. Sasase and Y. Ito, Formation of CuCl and AgCl nanoclusters by sequential implantation 206 (2003) 639
Takai, H., see Koguchi, Y. 206 (2003) 202
Takai, H., see Harada, N. 206 (2003) 308
Takai, M., see Angelov, Ch. 206 (2003) 907

Takai, O., see Watanabe, T. 206 (2003) 726
Takai, Y., see Matsunami, N. 206 (2003) 282
Takaki, K., see Mukaigawa, S. 206 (2003) 777
Takaki, K., S. Mukaigawa, T. Fujiwara, M. Kumagai and K. Yukimura, Characteristics of shunting arc discharge for carbon ion source 206 (2003) 794
Takaoka, G., see Aoki, T. 206 (2003) 855
Takaoka, G., see Aoki, T. 206 (2003) 861
Takaoka, G., see Nakatsu, O. 206 (2003) 866
Takaoka, G.H., see Nakai, A. 206 (2003) 842
Takaoka, G.H., see Seki, T. 206 (2003) 902
Takata, Y., see Sakaguchi, I. 206 (2003) 153
Takeda, Y., see Bandourko, V. 206 (2003) 606
Takeda, Y., see Okubo, N. 206 (2003) 610
Takeda, Y. and N. Kishimoto, Nonlinear optical properties of metal nanoparticle composites for optical applications 206 (2003) 620
Takeda, Y., see Kishimoto, N. 206 (2003) 634
Takeda, Y., see Suga, T. 206 (2003) 947
Takeuchi, M., Y. Onozaki, Y. Matsumura, H. Uchida and T. Kuji, Photoinduced hydrophilicity of TiO_2 thin film modified by Ar ion beam irradiation 206 (2003) 259
Takeuchi, M., see Yamashita, H. 206 (2003) 889
Takeuchi, M., see Yamashita, H. 206 (2003) 898
Takeuchi, T., see Matsutani, T. 206 (2003) 343
Takikawa, H., see Sakudo, N. 206 (2003) 687
Tan, I.H., see Ueda, M. 206 (2003) 760
Tanabe, H., see Nakamura, T. 206 (2003) 956
Tanaka, A., see Kitamura, S. 206 (2003) 548
Tanaka, A., see Yamaguchi, H. 206 (2003) 561
Tanaka, A., see Morishita, T. 206 (2003) 565
Tanaka, A., see Ishii, K. 206 (2003) 570
Tanaka, A., see Okamura, M. 206 (2003) 574
Tanaka, A., see Maekawa, M. 206 (2003) 579
Tanaka, A., see Watanabe, T. 206 (2003) 726
Tanaka, A., see Kurooka, S. 206 (2003) 1088
Tanaka, K., see Higuchi, T. 206 (2003) 103
Tanaka, S., see Umebayashi, T. 206 (2003) 264
Tanaka, S., see Yamamoto, S. 206 (2003) 268
Tanaka, T., see Saito, T. 206 (2003) 321
Tanaka, T., see Yoshida, M. 206 (2003) 712
Tanaka, T., S. Watanabe, G. Mizuno, T. Takagi, M. Yoshida, H. Horibe and K. Yukimura, Ion current extracted from a self ignition plasma around the target immersed in a pulsed rf ICP methane plasma . . . 206 (2003) 817
Tang, D.L., R.K.Y. Fu, X.B. Tian, P. Peng and P.K. Chu, Influence of magnetic field on magnetized hydrogen plasmas in plasma immersion ion implantation 206 (2003) 808
Tani, H., see Kasukabe, Y. 206 (2003) 390
Tani, S., see Suzuki, Y. 206 (2003) 538
Taniwaki, M., see Nitta, N. 206 (2003) 482
Tanoue, H., see Purwanto, S. 206 (2003) 326
Tao, M., see Oka, Y. 206 (2003) 700
Tarrant, R.N., see McKenzie, D.R. 206 (2003) 741
Tarus, J., see Nordlund, K. 206 (2003) 189
Tazawa, M., see Matsunami, N. 206 (2003) 282
Terai, T., see Kakiuchi, H. 206 (2003) 27
Terai, T., see Kakiuchi, H. 206 (2003) 237
Terashima, K., see Kobayashi, T. 206 (2003) 184
Terrasi, A., see De Salvador, D. 206 (2003) 922
Terry, J., see Donnelly, S.E. 206 (2003) 422
the ISOLDE Collaboration, see Weyer, G. 206 (2003) 90
Theodore, D., see Rangan, S. 206 (2003) 417

Thevuthasan, S., W. Jiang, V. Shutthanandan and W.J. Weber, Accumulation of ion beam induced disorder in strontium titanate 206 (2003) 162
Thompson, P.E., see Shao, L. 206 (2003) 413
Thorwarth, G., see Mändl, S. 206 (2003) 517
Tian, X.B., P. Peng and P.K. Chu, Numerical simulation of plasma implanted nitrogen depth profiles in iron 206 (2003) 673
Tian, X.B., see Li, L.H. 206 (2003) 691
Tian, X.B., see Tang, D.L. 206 (2003) 808
Tojo, H., Y. Mokuno, A. Chayahara, S. Iura, H. Kasai, N. Toyohara, T. Hidaka, S. Isogawa, M. Hijino and Y. Horino, Properties of diamond like carbon films by plasma based ion implantation and deposition method applying radio frequency wave and negative high voltage pulses through single feedthrough 206 (2003) 717
Torigoe, T., see Xu, G.C. 206 (2003) 362
Toriyama, T., see Hayashi, N. 206 (2003) 1066
Toyoda, N., see Yamada, I. 206 (2003) 820
Toyoda, N., see Birtcher, R.C. 206 (2003) 851
Toyoda, N., see Aoki, T. 206 (2003) 855
Toyoda, N., see Fujiwara, Y. 206 (2003) 870
Toyoda, N., Y. Fujiwara and I. Yamada, Stable optical thin film deposition with O_2 cluster ion beam assisted deposition 206 (2003) 875
Toyoda, N., see Kitagawa, T. 206 (2003) 884
Toyoda, N., see Miyauchi, K. 206 (2003) 893
Toyohara, N., see Tojo, H. 206 (2003) 717
Trautmann, C., see Papaléo, R.M. 206 (2003) 7
Trocellier, P., D. Gosset, D. Simeone, J.M. Costantini, X. Deschanels, D. Roudil, Y. Serruys, R. Grynszpan, S. Saudé and M. Beauvy, Application of nuclear reaction geometry for ^{3}He depth profiling in nuclear ceramics 206 (2003) 1077
Troitskiy, V.Yu., see Gerasimenko, N.N. 206 (2003) 299
Troitskiy, V.Yu., see Gerasimenko, N.N. 206 (2003) 644
Tsubakino, H., see Kanda, K. 206 (2003) 880
Tsubakino, H., see Kitagawa, T. 206 (2003) 884
Tsuda, O., see Watanabe, T. 206 (2003) 726
Tsuji, H., H. Sugahara, Y. Gotoh and J. Ishikawa, Improvement of photocatalytic efficiency of rutile titania by silver negative-ion implantation 206 (2003) 249
Tsuji, H., M. Izukawa, R. Ikeguchi, R. Kakinoki, H. Sato, Y. Gotoh and J. Ishikawa, Improvement of polydimethylsiloxane guide tube for nerve regeneration treatment by carbon negative-ion implantation . . 206 (2003) 507
Tsuji, H., N. Arai, M. Motono, Y. Gotoh, K. Adachi, H. Kotaki and J. Ishikawa, Study on optical reflection property from multilayer on Si substrate including nanoparticles in SiO_2 layer 206 (2003) 615
Tsuji, H., see Arai, N. 206 (2003) 629
Tsukamoto, T., see Yokoyama, Y. 206 (2003) 512
Tsukamoto, T., see Yotoriyama, T. 206 (2003) 527
Tsunoda, I., see Murakami, Y. 206 (2003) 304
Tu, Z.-L., Y. Kobayashi, K. Kiguchi and H. Watanabe, Irradiation effect of different heavy ions and track section on the silkworm *Bombyx mori* 206 (2003) 591

Ubagai, T., see Kobayashi, T. 206 (2003) 184
Uchida, H., see Abe, H. 206 (2003) 224
Uchida, H., see Takeuchi, M. 206 (2003) 259
Ueda, M., see Beloto, A.F. 206 (2003) 677
Ueda, M., G.F. Gomes, E. Abramof and H. Reuther, In-line nitrogen PIII/ion nitriding processing of metallic materials 206 (2003) 749
Ueda, M., I.H. Tan, R.S. Dallaqua, J.O. Rossi, J.J. Barroso and M.H. Tabacniks, Aluminum plasma immersion ion implantation in polymers 206 (2003) 760
Uedono, A., see Abe, H. 206 (2003) 224
Umarov, F.F., see Djurabekova, F.G. 206 (2003) 194
Umebayashi, T., see Yamaki, T. 206 (2003) 254
Umebayashi, T., T. Yamaki, T. Sumita, S. Yamamoto, S. Tanaka and K. Asai, UV-ray photoelectron and ab initio band calculation studies on electronic structures of Cr- or Nb-ion implanted titanium dioxide 206 (2003) 264
Umeda, N., see Bandourko, V. 206 (2003) 606
Umeda, N., see Okubo, N. 206 (2003) 610

Umeda, N., see Kishimoto, N. . . . 206 (2003) 634
Umeda, N., V.V. Bandourko, V.N. Vasilets and N. Kishimoto, Metal precipitation process in polymers induced by ion implantation of 60 keV Cu^- . . . 206 (2003) 657
Umeda, N., see Amekura, H. . . . 206 (2003) 1101
Umirzakov, B.E., see Djurabekova, F.G. . . . 206 (2003) 194
Ushida, K., see Kitajima, M. . . . 206 (2003) 99
Usmanov, T., see Stepanov, A.L. . . . 206 (2003) 624

Vacik, J., H. Naramoto, K. Narumi, S. Yamamoto and H. Abe, RBS and SEM analysis of the nickel–fullerene hybrid systems . . . 206 (2003) 395
Vagizov, F.G., see Khaibullin, R.I. . . . 206 (2003) 277
Vantomme, A., see Pipeleers, B. . . . 206 (2003) 95
Vantomme, A., see Alves, E. . . . 206 (2003) 1042
Varisco, P., see Milanez Silva, C. . . . 206 (2003) 486
Varoy, C.R., see Johnson, P.B. . . . 206 (2003) 1056
Vasilets, V.N., see Umeda, N. . . . 206 (2003) 657
Verda, R.D., M. Nastasi and R.W. Bower, Boron-induced redistribution of hydrogen implanted at elevated temperature into crystalline silicon . . . 206 (2003) 927
Vilaithong, T., see Yu, L.D. . . . 206 (2003) 586
Vishnyakov, V.M., see Donnelly, S.E. . . . 206 (2003) 422
Volz, K., see Ensinger, W. . . . 206 (2003) 334

Wada, M., S. Nishigaito, R. Flauta and T. Kasuya, Modification of bamboo surface by irradiation of ion beams 206 (2003) 557
Wada, S., M. Natsuhori, N. Ito, T. Funayama and Y. Kobayashi, Detection of DNA damage induced by heavy ion irradiation in the individual cells with comet assay . . . 206 (2003) 553
Wahl, U., see Bharuth-Ram, K. . . . 206 (2003) 941
Wahl, U., see Alves, E. . . . 206 (2003) 1042
Wahl, U., see Alves, E. . . . 206 (2003) 1047
Wakabayashi, H., see Hayashi, N. . . . 206 (2003) 1066
Wakahara, A., see Nakanishi, Y. . . . 206 (2003) 1033
Wakasa, T., see Mori, H. . . . 206 (2003) 31
Wakasa, T., see Onoda, S. . . . 206 (2003) 444
Wakasa, T., see Hirao, T. . . . 206 (2003) 457
Wakaya, F., see Itou, M. . . . 206 (2003) 1013
Wall, F.D., see Johnson, C.M. . . . 206 (2003) 1062
Wang, A., O. Ohashi, N. Yamaguchi, M. Aoki, Y. Higashi and N. Hitomi, Cleaning of diffusion bonding surface by argon ion bombardment treatment . . . 206 (2003) 219
Wang, C.M., see Jiang, W. . . . 206 (2003) 1037
Wang, J., see Yang, P. . . . 206 (2003) 721
Wang, L., see Zhang, Q.Y. . . . 206 (2003) 357
Wang, L.M., see Zhu, S. . . . 206 (2003) 1092
Wang, P.S., see Zhang, Q.Y. . . . 206 (2003) 357
Wang, Q., H. Ogiso, S. Nakano, J. Akedo and H. Ishikawa, Martensitic transformation and the stress induced by 3 MeV ion implantation in an austenite stainless steel sheet . . . 206 (2003) 118
Wang, X., see Feng, T. . . . 206 (2003) 198
Wang, X., see Shao, L. . . . 206 (2003) 413
Wang, Z.G., see Zhu, S. . . . 206 (2003) 1092
Watanabe, H., see Tu, Z.-L. . . . 206 (2003) 591
Watanabe, H. and M. Iwaki, In situ observation of Raman scattering from Ag- and W-ions implanted polyimide films during laser irradiation . . . 206 (2003) 1106
Watanabe, S., N.S. Ishioka, H. Shimomura, H. Muramatsu and T. Sekine, Dose dependence of the production yield of endohedral ^{133}Xe-fullerene by ion implantation . . . 206 (2003) 399
Watanabe, S., see Yoshida, M. . . . 206 (2003) 712
Watanabe, S., see Tanaka, T. . . . 206 (2003) 817
Watanabe, T., K. Yamamoto, O. Tsuda, A. Tanaka, Y. Koga and O. Takai, The influence of DC biasing on the uniformity of a-C:H films for three-dimensional substrates by using a plasma-based ion implantation technique . . . 206 (2003) 726

Weber, W.J., F. Gao, W. Jiang and Y. Zhang, Fundamental nature of ion–solid interactions in SiC 206 (2003) 1
Weber, W.J., see Thevuthasan, S. 206 (2003) 162
Weber, W.J., see Jiang, W. 206 (2003) 1037
Wei, P., Y. Xu, S. Nagata, K. Narumi and H. Naramoto, Structure and optical properties of germanium implanted with carbon ions 206 (2003) 233
Wendler, E., see Wesch, W. 206 (2003) 1018
Wendler, E., A. Kamarou, E. Alves, K. Gärtner and W. Wesch, Three-step amorphisation process in ion-implanted GaN at 15 K 206 (2003) 1028
Wesch, W., A. Kamarou, E. Wendler, K. Gärtner, P.I. Gaiduk and S. Klaumünzer, Ionisation stimulated defect annealing in GaAs and InP 206 (2003) 1018
Wesch, W., see Wendler, E. 206 (2003) 1028
Weyer, G., H.P. Gunnlaugsson, M. Dietrich, M. Fanciulli, K. Bharuth-Ram, R. Sielemann and the ISOLDE Collaboration, Creation and annealing of defect structures in silicon-based semiconductors during and after implantations at 77–500 K 206 (2003) 90
Whang, C.N., see Jeon, G.Y. 206 (2003) 409
Whang, C.-N., see Lee, I.-S. 206 (2003) 522
Williams, J.S., see Ruault, M.-O. 206 (2003) 912
Wong, S.P., see Gao, Y. 206 (2003) 317
Wu, X., see Zhang, X. 206 (2003) 215
Wu, X., see Zhang, X. 206 (2003) 382

Xiang, X., see Zhu, S. 206 (2003) 1092
Xu, G.C., Y. Hibino, K. Kurotobi, Y. Suzuki and M. Iwaki, Hydrogen contents and related properties of a-C:H formed with unbalanced magnetron sputtering 206 (2003) 330
Xu, G.C., K. Fujita, T. Torigoe and Y. Hibino, The microstructures of yttria-stabilized zirconia deposited with ion-plating apparatus 206 (2003) 362
Xu, J., see Feng, T. 206 (2003) 198
Xu, J.J., see Zhang, Q.Y. 206 (2003) 357
Xu, Q., T. Yoshiie and H.C. Huang, Molecular dynamics simulation of vacancy diffusion in tungsten induced by irradiation 206 (2003) 123
Xu, Y., see Wei, P. 206 (2003) 233

Yamada, I., J. Matsuo, N. Toyoda and Collaborative Research Centre for Cluster Ion Beam Process Technology, Cluster ion beam process technology 206 (2003) 820
Yamada, I., see Matsuo, J. 206 (2003) 838
Yamada, I., see Nakai, A. 206 (2003) 842
Yamada, I., see Insepov, Z. 206 (2003) 846
Yamada, I., see Birtcher, R.C. 206 (2003) 851
Yamada, I., see Aoki, T. 206 (2003) 855
Yamada, I., see Aoki, T. 206 (2003) 861
Yamada, I., see Nakatsu, O. 206 (2003) 866
Yamada, I., see Fujiwara, Y. 206 (2003) 870
Yamada, I., see Toyoda, N. 206 (2003) 875
Yamada, I., see Kanda, K. 206 (2003) 880
Yamada, I., see Kitagawa, T. 206 (2003) 884
Yamada, I., see Miyauchi, K. 206 (2003) 893
Yamada, I., see Seki, T. 206 (2003) 902
Yamada, Y., see Kasukabe, Y. 206 (2003) 390
Yamada, Y., see Ishii, K. 206 (2003) 570
Yamaguchi, H., S. Nagatomi, T. Morishita, K. Degi, A. Tanaka, N. Shikazono and Y. Hase, Mutation induced with ion beam irradiation in rose 206 (2003) 561
Yamaguchi, H., see Morishita, T. 206 (2003) 565
Yamaguchi, K., see Haraguchi, M. 206 (2003) 313
Yamaguchi, K., see Saito, T. 206 (2003) 321
Yamaguchi, N., see Wang, A. 206 (2003) 219
Yamakawa, T., see Mori, H. 206 (2003) 31
Yamaki, D., see Nakazawa, T. 206 (2003) 166
Yamaki, T., see Sumita, T. 206 (2003) 245

Yamaki, T., T. Umebayashi, T. Sumita, S. Yamamoto, M. Maekawa, A. Kawasuso and H. Itoh, Fluorine-doping in titanium dioxide by ion implantation technique 206 (2003) 254
Yamaki, T., see Umebayashi, T. 206 (2003) 264
Yamaki, T., see Yamamoto, S. 206 (2003) 268
Yamamoto, H. and T. Saito, Fabrication and stability of binary clusters by reactive molecular ion irradiation 206 (2003) 42
Yamamoto, H., see Haraguchi, M. 206 (2003) 313
Yamamoto, H., see Saito, T. 206 (2003) 321
Yamamoto, K., see Watanabe, T. 206 (2003) 726
Yamamoto, S., see Ookawa, R. 206 (2003) 175
Yamamoto, S., see Takahiro, K. 206 (2003) 206
Yamamoto, S., see Choi, Y. 206 (2003) 241
Yamamoto, S., see Sumita, T. 206 (2003) 245
Yamamoto, S., see Yamaki, T. 206 (2003) 254
Yamamoto, S., see Umebayashi, T. 206 (2003) 264
Yamamoto, S., T. Yamaki, H. Naramoto and S. Tanaka, Characterization of metal-doped TiO_2 films by RBS/channeling 206 (2003) 268
Yamamoto, S., see Vacik, J. 206 (2003) 395
Yamamoto, S., see Takahiro, K. 206 (2003) 639
Yamamoto, S., see Kitazawa, S.-i. 206 (2003) 952
Yamamoto, Y., see Koguchi, Y. 206 (2003) 202
Yamamoto, Y., see Kitahara, N. 206 (2003) 999
Yamashita, H., M. Harada, J. Misaka, H. Nakao, M. Takeuchi and M. Anpo, Application of ion beams for preparation of TiO_2 thin film photocatalysts operatable under visible light irradiation: Ion-assisted deposition and metal ion-implantation 206 (2003) 889
Yamashita, H., H. Nakao, M. Takeuchi, Y. Nakatani and M. Anpo, Coating of TiO_2 photocatalysts on super-hydrophobic porous teflon membrane by an ion assisted deposition method and their self-cleaning performance 206 (2003) 898
Yamashita, M., see Lim, J.-W. 206 (2003) 371
Yanagisawa, J., see Itou, M. 206 (2003) 1013
Yang, P., S.C.H. Kwok, P.K. Chu, Y.X. Leng, J.Y. Chen, J. Wang and N. Huang, Haemocompatibility of hydrogenated amorphous carbon (a-C:H) films synthesized by plasma immersion ion implantation-deposition 206 (2003) 721
Yasuda, K., see Higuchi, T. 206 (2003) 103
Yasuno, N., see Okamura, M. 206 (2003) 574
Yatsuzuka, M., see Nishimura, Y. 206 (2003) 696
Yatsuzuka, M., see Oka, Y. 206 (2003) 700
Yi, Z., see Zhang, X. 206 (2003) 382
Yokota, K., K. Nakamura, T. Kasuya and M. Ohnishi, Phase composition and crystalline structure of titanium nitride deposited on silicon by an ion-beam assisted deposition technique 206 (2003) 386
Yokoyama, Y., see Nakao, A. 206 (2003) 211
Yokoyama, Y., T. Tsukamoto, T. Kobayashi and M. Iwaki, Immobilization of collagen by ion bombardment 206 (2003) 512
Yoneda, R., see Sakudo, N. 206 (2003) 687
Yoshida, A., see Nakanishi, Y. 206 (2003) 1033
Yoshida, M., S. Watanabe, T. Tanaka, T. Takagi, M. Shinohara and J.W. Lee, Investigation of diamond-like carbon formed on PET film by plasma-source ion implantation using C_2H_2 and CH_4 ..... 206 (2003) 712
Yoshida, M., see Tanaka, T. 206 (2003) 817
Yoshiie, T., see Xu, Q. 206 (2003) 123
Yoshitake, T., see Murakami, Y. 206 (2003) 304
Yotoriyama, T., T. Tsukamoto, Y. Suzuki and M. Iwaki, Formation of a super-thin film and a self-assembly cellular sheet by ion-beam irradiation 206 (2003) 527
Yu, K.M., see de M. Azevedo, G. 206 (2003) 1024
Yu, L.D., T. Vilaithong, B. Phanchaisri, P. Apavatjrut, S. Anuntalabhochai, P. Evans and I.G. Brown, Ion penetration depth in the plant cell wall 206 (2003) 586
Yu, Y.H., see Li, W.J. 206 (2003) 339
Yuba, Y., S. Hazama and K. Gamo, Nanostructure fabrication of InP by low energy ion beams 206 (2003) 648
Yuba, Y., see Itou, M. 206 (2003) 1013
Yugo, S., see Fukudome, T. 206 (2003) 287

Yukimura, K., see Masamune, S. 206 (2003) 682
Yukimura, K., T. Muraho, M. Kumagai, H. Saito, M. Kohata and T. Maruyama, Effects of pressure on the structure of titanium nitride film in the preparation using metallic plasma-based ion implantation and deposition 206 (2003) 745
Yukimura, K., see Ikehata, T. 206 (2003) 772
Yukimura, K., see Ma, X.X. 206 (2003) 787
Yukimura, K. and T. Muraho, A two-switch mode pulse modulator for plasma-based ion implantation and deposition 206 (2003) 791
Yukimura, K., see Takaki, K. 206 (2003) 794
Yukimura, K., see Ma, X.X. 206 (2003) 813
Yukimura, K., see Tanaka, T. 206 (2003) 817

Zalar, A., see Piatkowska, A. 206 (2003) 1052
Zawislak, F., see Kling, A. 206 (2003) 653
Zeilhofer, H.-F., see Mändl, S. 206 (2003) 517
Zhang, C., see Lu, H.F. 206 (2003) 22
Zhang, H., see Zhang, X. 206 (2003) 215
Zhang, H., see Zhang, X. 206 (2003) 382
Zhang, H.Q., see Li, L.H. 206 (2003) 691
Zhang, Q.Y., see Lu, H.F. 206 (2003) 22
Zhang, Q.Y., W.J. Zhao, P.S. Wang, L. Wang, J.J. Xu and P.K. Chu, Microstructure, morphology and their annealing behaviors of alumina films synthesized by ion beam assisted deposition 206 (2003) 357
Zhang, T., see Zhang, X. 206 (2003) 215
Zhang, T., see Zhang, X. 206 (2003) 382
Zhang, X., see Zhang, X 206 (2003) 215
Zhang, X., H. Zhang, X. Wu, T. Zhang, X. Zhang and J. Sang, Structure and wear resistance of tetrahedral amorphous carbon films 206 (2003) 215
Zhang, X., X. Wu, Z. Yi, T. Zhang and H. Zhang, The TiN/AlN multilayers deposited by filtered vacuum arc deposition 206 (2003) 382
Zhang, Y., see Weber, W.J. 206 (2003) 1
Zhang, Y.H., see Li, L.H. 206 (2003) 691
Zhao, W.J., see Zhang, Q.Y. 206 (2003) 357
Zheglov, E.P., see Khaibullin, R.I. 206 (2003) 1115
Zhikharev, V.A., see Khaibullin, R.I. 206 (2003) 1115
Zhu, S., X.T. Zu, X. Xiang, Z.G. Wang, L.M. Wang and R.C. Ewing, Electron microscopy and optical spectroscopy study of xenon-implanted yttria-stabilized zirconia 206 (2003) 1092
Zou, S., see Feng, T. 206 (2003) 198
Zou, S.C., see Li, W.J. 206 (2003) 339
Zu, X.T., see Zhu, S. 206 (2003) 1092